



**VARIOUS ELECTRICAL-AND-THERMOELECTRIC LAWS,
RELATIONS AND COEFFICIENTS IN NEW n(p)-TYPE
DEGENERATE “COMPENSATED” GaAs(1-x)Sb(x)-CRYSTALLINE
ALLOY, ENHANCED BY OUR STATIC DIELECTRIC CONSTANT
LAW, ACCURATE FERMI ENERGY, AND ELECTRICAL
CONDUCTIVITY MODEL (X)**

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ABSTRACT

In the $n^+(p^+) - p(n) X(x) \equiv \text{GaAs}_{1-x}\text{Sb}_x$ - crystalline alloy, $0 \leq x \leq 1$, various electrical-and-thermoelectric laws, relations and coefficients, enhanced by our static dielectric constant law given in Equations (1a, 1b), being due to the effects of the size of donor (acceptor) $d(a)$ -radius $r_{d(a)}$ and the x -concentration, by our accurate Fermi energy given in Eq. (11), and finally by our electrical conductivity model given in Eq. (14), are now investigated, basing on the same physical model and mathematical treatment method, as those used in our recent works.^[1, 2] It should be noted here that, for $x=0$, these obtained numerical results are reduced to those given in the n(p)-type degenerate GaAs-crystal.^[4] Then, some remarkable results could be cited in the following. In

Tables 5n(5p) given Appendix 1, for a given impurity density N and with increasing temperature T , and then in Tables 6n(6p) given Appendix 1, for a given T and with decreasing N , the reduced Fermi-energy $\xi_{n(p)}$ decreases, and other thermoelectric coefficients are in variations, as indicated by the arrows by: (increase: ↑, decrease: ↓). Further, one notes in these Tables that, for any given x , $r_{d(a)}$ and N (or T), with increasing T (or decreasing N)

one obtains: (i) for $\xi_{n(p)} \simeq 1.8138$, while the numerical results of the Seebeck coefficient S present a same minimum $(S)_{\min} (\simeq -1.563 \times 10^{-4} \frac{V}{K})$, those of the figure of merit ZT show a same maximum $(ZT)_{\max} = 1$, (ii) for $\xi_{n(p)} = 1$, the numerical results of S, ZT, the Mott figure of merit $(ZT)_{Mott}$, the first Van-Cong coefficient VC1, and the Thomson coefficient Ts, present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$, respectively, and finally (iii) for $\xi_n \simeq 1.8138$, $(ZT)_{Mott} = 1$. It seems that these same obtained results could represent **a new law for the thermoelectric properties, obtained in the degenerate case ($\xi_{n(p)} \geq 0$)**.

KEYWORDS: Electrical conductivity, Seebeck coefficient (S), Figure of merit (ZT), First Van-Cong coefficient (VC1), Second Van-Cong coefficient (VC2), Thomson coefficient (Ts), Peltier coefficient (Pt)

INTRODUCTION

In the $n^+(p^+) - p(n) X(x) \equiv GaAs_{1-x}Sb_x$ - crystalline alloy, $0 \leq x \leq 1$, the electrical-and-thermoelectric laws, relations, and various coefficients, enhanced by our static dielectric constant law, $\epsilon(r_{d(a)}, x)$, $r_{d(a)}$ being the donor (acceptor) d(a)-radius, given in Equations (1a, 1b) and our electrical conductivity model, in Eq. (14), and also by our accurate Fermi energy, $E_{Fn(Fp)}$, given in Eq. (11), are now investigated, by basing on the same physical model and mathematical treatment method, as those used in our recent works.^[1, 2] It should be noted here that for $x=0$, these obtained numerical results may be reduced to those given in the n(p)-type degenerate GaAs-crystal.^[3-7] Then, some remarkable results could be noted in the following.

(1) The generalized Mott criterium in the metal-insulator transition (MIT) is expressed in Equations (3, 5, 6), stating that the critical impurity density $N_{CDn(CDp)}$ is just the density of electrons (holes), localized in the exponential conduction (valence)-band tail (EBT), $N_{CDn(CDp)}^{EBT}$, obtained with a precision of the order of 2.9×10^{-7} , as given in our recent work (Van Cong, 2024), and the effective electron (hole)-density can be defined by: $N^* \equiv N - N_{CDn(CDp)} \simeq N - N_{CDn(CDp)}^{EBT}$, N being the total impurity density, as that observed in the compensated crystals.

(2) The ratio of the inverse effective screening length $k_{sn(sp)}$ to Fermi wave number $k_{Fn(kp)}$ at 0 K, $R_{sn(sp)}(N^*)$, defined in Eq. (7), is valid at any N^* .

(3) The Fermi energy for any N and T, $E_{Fn(Fp)}$, determined in Eq. (11) with a precision of the order of 2.11×10^{-4} [7], and it is present in all the expressions of electrical-and-thermoelectric coefficients.

(4) Our expressions for the electrical conductivity, σ , and for the Seebeck coefficient, S, determined respectively in Equations (14, 19) are the basic expressions, used to determine all the following electrical-and-thermoelectric coefficients.

(5) In Tables 5n(5p) given Appendix 1, for a given impurity density N and with increasing temperature T, and further in Tables 6n(6p) given Appendix 1, for a given T and with decreasing N, the reduced Fermi-energy $\xi_{n(p)}$ decreases, and other thermoelectric coefficients are in variations, as indicated by the arrows by: (increase: ↗, decrease: ↘). Furthermore, one notes in these Tables that, for any given x, $r_{d(a)}$ and N (or T), with increasing T (or decreasing N), one obtains: (i) for $\xi_{n(p)} \simeq 1.8138$, while the numerical results of the Seebeck coefficient S present a same minimum $(S)_{min.} (\simeq -1.563 \times 10^{-4} \frac{V}{K})$, those of the figure of merit ZT show a same maximum $(ZT)_{max.} = 1$, (ii) for $\xi_{n(p)} = 1$, the numerical results of S, ZT, the Mott figure of merit $(ZT)_{Mott}$, the first Van-Cong coefficient VC1, and the Thomson coefficient T_s , present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$, respectively, and finally (iii) for $\xi_n \simeq 1.8138$, $(ZT)_{Mott} = 1$. It seems that these same results could represent **a new law for the thermoelectric properties, obtained in the degenerate case ($\xi_{n(p)} \geq 0$)**.

OUR STATIC DIELECTRIC CONSTANT LAW AND GENERALIZED MOTT CRITERIUM IN THE METAL-INSULATOR TRANSITION

First of all, in the $n^+(p^+) - p(n)$ X(x) \equiv GaAs_{1-x}Sb_x crystalline alloy at T=0 K, we denote the donor (acceptor) d(a)-radius by $r_{d(a)}$, the corresponding intrinsic one by: $r_{do(ao)} = r_{As(Ga)}$, the unperturbed relative effective electron (hole) mass in conduction (valence) bands by: $m_{c(v)}(x)/m_o$, the unperturbed relative static dielectric constant by: $\epsilon_o(x)$, and the intrinsic band gap by: $E_{go}(x)$. Then, their values are reported in Table 1 in Appendix 1.

Therefore, we can define the effective donor (acceptor)-ionization energy in absolute values as:

$$E_{do(ao)}(x) = \frac{13600 \times [m_c(v)(x)/m_0]}{[\varepsilon_0(x)]^2} \text{ meV} , \quad \text{and then, the isothermal bulk modulus, by:}$$

$$B_{do(ao)}(x) \equiv \frac{E_{do(ao)}(x)}{\left(\frac{4\pi}{3}\right) \times (r_{do(ao)})^3}.$$

Our Static Dielectric Constant Law

Here, the changes in all the energy-band-structure parameters, expressed in terms of the effective relative dielectric constant $\varepsilon(r_{d(a)}, x)$, developed as follows.

At $r_{d(a)} = r_{do(ao)}$, the needed boundary conditions are found to be, for the impurity-atom volume $V = (4\pi/3) \times (r_{d(a)})^3$, $V_{do(ao)} = (4\pi/3) \times (r_{do(ao)})^3$, for the pressure p , $p_o = 0$, and for the deformation potential energy (or the strain energy) α , $\alpha_o = 0$. Further, the two important equations, used to determine the α -variation, $\Delta \alpha \equiv \alpha - \alpha_o = \alpha$, are defined by:

$$\frac{dp}{dV} = -\frac{B}{V} \text{ and } p = -\frac{d\alpha}{dV}, \text{ giving rise to: } \frac{d}{dV} \left(\frac{d\alpha}{dV} \right) = \frac{B}{V}. \text{ Then, by an integration, one gets:}$$

$$[\Delta\alpha(r_{d(a)}, x)]_{n(p)} = B_{do(ao)}(x) \times (V - V_{do(ao)}) \times \ln \left(\frac{V}{V_{do(ao)}} \right) = E_{do(ao)}(x) \times \left[\left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 - 1 \right] \times \ln \left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 \geq 0.$$

Furthermore, we also showed that, as $r_{d(a)} > r_{do(ao)}$ ($r_{d(a)} < r_{do(ao)}$), the compression (dilatation) gives rise to the increase (the decrease) in the energy gap $E_{gno(gpo)}(r_{d(a)}, x)$, and the effective donor (acceptor)-ionization energy $E_{d(a)}(r_{d(a)}, x)$ in absolute values, obtained in the effective Bohr model, which is represented respectively by: $\pm [\Delta\alpha(r_{d(a)}, x)]_{n(p)}$,

$$E_{gno(gpo)}(r_{d(a)}, x) - E_{go}(x) = E_{d(a)}(r_{d(a)}, x) - E_{do(ao)}(x) = E_{do(ao)}(x) \times \left[\left(\frac{\varepsilon_0(x)}{\varepsilon(r_{d(a)})} \right)^2 - 1 \right] = \\ + [\Delta\alpha(r_{d(a)}, x)]_{n(p)},$$

for $r_{d(a)} \geq r_{do(ao)}$, and for $r_{d(a)} \leq r_{do(ao)}$,

$$E_{gno(gpo)}(r_{d(a)}, x) - E_{go}(x) = E_{d(a)}(r_{d(a)}, x) - E_{do(ao)}(x) = E_{do(ao)}(x) \times \left[\left(\frac{\varepsilon_0(x)}{\varepsilon(r_{d(a)})} \right)^2 - 1 \right] = \\ - [\Delta\alpha(r_{d(a)}, x)]_{n(p)}.$$

Therefore, one obtains the expressions for relative dielectric constant $\varepsilon(r_{d(a)}, x)$ and energy band gap $E_{gn(gp)}(r_{d(a)}, x)$, as:

(i)-for $r_{d(a)} \geq r_{do(ao)}$, since $\varepsilon(r_{d(a)}, x) = \frac{\varepsilon_0(x)}{\sqrt{1 + \left[\left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 - 1 \right] \times \ln \left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3}} \leq \varepsilon_0(x)$, being a new **$\varepsilon(r_{d(a)}, x)$ -law**,

$$E_{gn(gp)}(r_{d(a)}, x) - E_{go}(x) = E_{d(a)}(r_{d(a)}, x) - E_{do(ao)}(x) = E_{do(ao)}(x) \times \left[\left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 - 1 \right] \times \ln \left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 \geq 0, \quad (1a)$$

according to the increase in both $E_{gn(gp)}(r_{d(a)}, x)$ and $E_{d(a)}(r_{d(a)}, x)$, with increasing $r_{d(a)}$ and for a given x , and

(ii)-for $r_{d(a)} \leq r_{do(ao)}$, since $\varepsilon(r_{d(a)}, x) = \frac{\varepsilon_0(x)}{\sqrt{1 - \left[\left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 - 1 \right] \times \ln \left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3}} \geq \varepsilon_0(x)$, with a condition, given by: $\left[\left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 - 1 \right] \times \ln \left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 < 1$, being a new **$\varepsilon(r_{d(a)}, x)$ -law**,

$$E_{gn(gp)}(r_{d(a)}, x) - E_{go}(x) = E_{d(a)}(r_{d(a)}, x) - E_{do(ao)}(x) = -E_{do(ao)}(x) \times \left[\left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 - 1 \right] \times \ln \left(\frac{r_{d(a)}}{r_{do(ao)}} \right)^3 \leq 0, \quad (1b)$$

corresponding to the decrease in both $E_{gn(gp)}$ and $E_{d(a)}$, with decreasing $r_{d(a)}$ and for a given x .

It should be noted that, in the following, all the electrical-and-thermoelectric properties strongly depend on this **new $\varepsilon(r_{d(a)}, x)$ -law**.

Furthermore, the effective Bohr radius $a_{Bn(Bp)}(r_{d(a)}, x)$ is defined by:

$$a_{Bn(Bp)}(r_{d(a)}, x) \equiv \frac{\varepsilon(r_{d(a)}, x) \times \hbar^2}{m_{C(v)}(x) \times m_0 \times q^2} = 0.53 \times 10^{-8} \text{ cm} \times \frac{\varepsilon(r_{d(a)}, x)}{m_{C(v)}(x)}. \quad (2)$$

Generalized Mott Criterium in the MIT

Now, it is interesting to remark that the critical total donor (acceptor)-density in the MIT at T=0 K, $N_{CDn(CDp)}(r_{d(a)}, x)$, was given by the Mott's criterium, with an empirical parameter, $M_{n(p)}$, as [2]:

$$N_{CDn(CDp)}(r_{d(a)}, x)^{1/3} \times a_{Bn(Bp)}(r_{d(a)}, x) = M_{n(p)}, M_{n(p)} = 0.25, \quad (3)$$

depending thus on our **new $\varepsilon(r_{d(a)}, x)$ -law**.

This excellent one can be explained from the definition of the reduced effective Wigner-Seitz (**WS**) radius $r_{sn(sp)}$, characteristic of interactions, by:

$$r_{sn(sp)}(N, r_{d(a)}, x) \equiv \left(\frac{3}{4\pi N}\right)^{1/3} \times \frac{1}{a_{Bn(Bp)}(r_{d(a)}, x)} = 1.1723 \times 10^8 \times \left(\frac{1}{N}\right)^{1/3} \times \frac{m_{c(v)}(x) \times m_0}{\varepsilon(r_{d(a)}, x)}, \quad (4)$$

being equal to, in particular, at $N = N_{CDn(CDp)}(r_{d(a)}, x)$: $r_{sn(sp)}(N_{CDn(CDp)}(r_{d(a)}, x), r_{d(a)}, x) = 2.4813963$, for any $(r_{d(a)}, x)$ -values. Then, from Eq. (4), one also has :

$$N_{CDn(CDp)}(r_{d(a)}, x)^{1/3} \times a_{Bn(Bp)}(r_{d(a)}, x) = \left(\frac{3}{4\pi}\right)^{\frac{1}{3}} \times \frac{1}{2.4813963} = 0.25 = (WS)_{n(p)} = M_{n(p)}, \quad (5)$$

explaining thus the existence of the Mott's criterium.

Furthermore, by using $M_{n(p)} = 0.25$, according to the empirical Heisenberg parameter $\mathcal{H}_{n(p)} = 0.47137$, as those given in our previous work^[2], we have also showed that $N_{CDn(CDp)}$ is just **the density of electrons (holes) localized in the exponential conduction (valence)-band tail**, $N_{CDn(CDp)}^{EBT}$, with a precision of the order of 2.9×10^{-7} .^[2]

It should be noted that the values of $M_{n(p)}$ and $\mathcal{H}_{n(p)}$ could be chosen so that those of $N_{CDn(CDp)}$ and $N_{CDn(CDp)}^{EBT}$ are found to be in good agreement with their experimental results.

Therefore, the density of electrons (holes) given in parabolic conduction (valence) bands can be defined, as that given in compensated materials:

$$N^*(N, r_{d(a)}, x) \equiv N - N_{CDn(NDp)}(r_{d(a)}, x) = N^*, \text{ for a presentation simplicity.} \quad (6)$$

In summary, as observed in Table 5 of our previous paper [2], one remarks that, for a given x and an increasing $r_{d(a)}$, $\varepsilon(r_{d(a)}, x)$ decreases, while $E_{gno(gpo)}(r_{d(a)}, x)$, $N_{CDn(NDp)}(r_{d(a)}, x)$ and $N_{CDn(CDp)}^{EBT}(r_{d(a)}, x)$ increase, affecting strongly all electrical-and-thermoelectric properties, as those observed in following Sections.

PHYSICAL MODEL

In the $n^+(p^+) - p(n) X(x)$ - crystalline alloy, if denoting the Fermi wave number by:

$k_{Fn(Fp)}(N^*) \equiv \left(\frac{3\pi^2 N^*}{E_{c(v)}}\right)^{\frac{1}{3}}$, the reduced effective Wigner-Seitz (**WS**) radius $r_{sn(sp)}$, characteristic of interactions, being given in Eq. (4), in which N is replaced by N^* , is now defined by:

$$\gamma \times r_{sn(sp)}(N^*) \equiv \frac{k_{Fn(Fp)}^{-1}}{a_{Bn(Bp)}} < 1,$$

being proportional to $N^{*-1/3}$. Here, $\gamma = (4/9\pi)^{1/3}$, $k_{Fn(Fp)}^{-1}$ means the averaged distance between ionized donors (acceptors), and $a_{Bn(Bp)}(r_{d(a)}, x)$ is determined in Eq. (2).

Then, the ratio of the inverse effective screening length $k_{sn(sp)}$ to Fermi wave number $k_{Fn(kp)}$ at 0 K is defined by:

$$R_{sn(sp)}(N^*) \equiv \frac{k_{sn(sp)}}{k_{Fn(Fp)}} = \frac{k_{Fn(Fp)}^{-1}}{k_{sn(sp)}^{-1}} = R_{snWS(spWS)} + [R_{snTF(spTF)} - R_{snWS(spWS)}] e^{-r_{sn(sp)}} < 1, \quad (7)$$

being valid at any N^* .

Here, these ratios, $R_{snTF(spTF)}$ and $R_{snWS(spWS)}$, can be determined as follows.

First, for $N \gg N_{CDn(NDp)}(r_{d(a)}, x)$, according to the **Thomas-Fermi (TF)-approximation**, the ratio $R_{snTF(spTF)}(N^*)$ is reduced to

$$R_{snTF(spTF)}(N^*) \equiv \frac{k_{snTF(spTF)}}{k_{Fn(Fp)}} = \frac{k_{Fn(Fp)}^{-1}}{k_{snTF(spTF)}^{-1}} = \sqrt{\frac{4\gamma r_{sn(sp)}}{\pi}} \ll 1, \quad (8)$$

being proportional to $N^{*-1/6}$.

Secondly, for $N \ll N_{CDn(NDp)}(r_{d(a)})$, according to the **Wigner-Seitz (WS)-approximation**, the ratio $R_{snWS(snWS)}$ is respectively reduced to

$$R_{sn(sp)WS}(N^*) \equiv \frac{k_{sn(sp)WS}}{k_{Fn}} = 0.5 \times \left(\frac{s}{2\pi} - \gamma \frac{d[r_{sn(sp)}^2 \times E_{CE}(N^*)]}{dr_{sn(sp)}} \right), \quad (9)$$

where $E_{CE}(N^*)$ is the majority-carrier correlation energy (CE), being determined by:

$$E_{CE}(N^*) = \frac{-0.87553}{0.0908 + r_{sn(sp)}} + \frac{\frac{0.87553}{0.0908 + r_{sn(sp)}} + \left(\frac{2[1 - \ln(2)]}{\pi^2} \right) \times \ln(r_{sn(sp)}) - 0.093288}{1 + 0.03847728 \times r_{sn(sp)}^{1.67378876}}.$$

Furthermore, in the highly degenerate case, the physical conditions are found to be given by:

$$\frac{k_{Fn(Fp)}^{-1}}{a_{Bn(Bp)}} < \frac{\eta_{n(p)}}{E_{Fno(Fpo)}} \equiv \frac{1}{A_{n(p)}} < \frac{k_{Fn(Fp)}^{-1}}{k_{sn(sp)}^{-1}} \equiv R_{sn(sp)} < 1, \quad \eta_{n(p)}(N^*) \equiv \frac{\sqrt{2\pi N^*}}{\epsilon(r_{d(a)})} \times q^2 k_{sn(sp)}^{-1/2}, \quad (10)$$

which gives: $A_{n(p)}(N^*) = \frac{E_{Fno(Fpo)}(N^*)}{\eta_{n(p)}(N^*)}$.

FERMI ENERGY AND FERMI-DIRAC DISTRIBUTION FUNCTION

Fermi Energy

Here, for a presentation simplicity, we change all the sign of various parameters, given in the $p^+ - X(x)$ - crystalline alloy in order to obtain the same one, as given in the $n^+ - X(x)$ -

crystalline alloy, according to the reduced Fermi energy $E_{Fn(Fp)}$, $\xi_{n(p)}(N, r_{d(a)}, x, T) \equiv \frac{E_{Fn(Fp)}(N, r_{d(a)}, x, T)}{k_B T} > 0 (< 0)$, obtained respectively in the degenerate (non-degenerate) case.

For any $(N, r_{d(a)}, x, T)$, the reduced Fermi energy $\xi_{n(p)}(N, r_{d(a)}, x, T)$ or the Fermi energy $E_{Fn(Fp)}(N, r_{d(a)}, x, T)$, obtained in our previous paper^[7], obtained with a precision of the order of 2.11×10^{-4} , is found to be given by:

$$\xi_{n(p)}(u) \equiv \frac{E_{Fn(Fp)}(u)}{k_B T} = \frac{G(u) + A u^B F(u)}{1 + A u^B} \equiv \frac{V(u)}{W(u)}, A = 0.0005372 \text{ and } B = 4.82842262, \quad (11)$$

where u is the reduced electron density, $u(N, r_{d(a)}, x, T) \equiv \frac{N^*}{N_{c(v)}(T, x)}$, $N_{c(v)}(T, x) = 2g_{c(v)} \times \left(\frac{m_{c(v)}(x) \times m_o \times k_B T}{2\pi\hbar^2}\right)^{\frac{3}{2}} (\text{cm}^{-3})$, $g_{c(v)} = 1$, $F(u) = au^{\frac{2}{3}} \left(1 + bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}}\right)^{-\frac{2}{3}}$, $a = [3\sqrt{\pi}/4]^{2/3}$, $b = \frac{1}{8} \left(\frac{\pi}{a}\right)^2$, $c = \frac{62.3739855}{1920} \left(\frac{\pi}{a}\right)^4$, and $G(u) \simeq \ln(u) + 2^{-\frac{3}{2}} \times u \times e^{-du}$; $d = 2^{3/2} \left[\frac{1}{\sqrt{27}} - \frac{5}{16}\right] > 0$.

So, in the non-degenerate case ($u \ll 1$), one has: $E_{Fn(Fp)}(u) = k_B T \times G(u) \simeq k_B T \times \ln(u)$ as $u \rightarrow 0$, **the limiting non-degenerate condition**, and in the very degenerate case ($u \gg 1$), one

gets: $E_{Fn(Fp)}(u \gg 1) = k_B T \times F(u) = k_B T \times au^{\frac{2}{3}} \left(1 + bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}}\right)^{-\frac{2}{3}} \simeq \frac{\hbar^2 \times k_{Fn(Fp)}^2(N^*)}{2 \times m_{c(v)}(x) \times m_o}$ as $u \rightarrow \infty$,

the limiting degenerate condition. In other words, $\xi_{n(p)} \equiv \frac{E_{Fn(Fp)}}{k_B T}$ is accurate, and it also verifies the correct limiting conditions.

In particular, at $T=0K$, since $u^{-1} = 0$, Eq. (11) is reduced to: $E_{Fn(Fp)}(N^*) \equiv \frac{\hbar^2 \times k_{Fn(Fp)}^2(N^*)}{2 \times m_{c(v)}(x) \times m_o}$, being proportional to $(N^*)^{2/3}$, and also equal to 0 at $N^* = 0$, according to the MIT.

In the following, it should be noted that all the electrical-and-thermoelectric properties strongly depend on such the accurate expression of $\xi_{n(p)}(N, r_{d(a)}, x, T)$.^[2]

Fermi-Dirac Distribution Function (FDDF)

The Fermi-Dirac distribution function (FDDF) is given by: $f(E) \equiv (1 + e^\gamma)^{-1}$, $\gamma \equiv (E - E_{Fn(Fp)})/(k_B T)$.

So, the average of E^p , calculated using the FDDF-method, as developed in our previous works^[1, 3] is found to be given by:

$$\langle E^p \rangle_{FDDF} \equiv G_p(E_{Fn(Fp)}) \times E_{Fn(Fp)}^p \equiv \int_{-\infty}^{\infty} E^p \times \left(-\frac{\partial f}{\partial E} \right) dE, \quad -\frac{\partial f}{\partial E} = \frac{1}{k_B T} \times \frac{e^\gamma}{(1+e^\gamma)^2}.$$

Further, one notes that, at 0 K, $-\frac{\partial f}{\partial E} = \delta(E - E_{Fn(Fp)})$, $\delta(E - E_{Fn(Fp)})$ being the Dirac delta (δ)-function. Therefore, $G_p(E_{Fn(Fp)}) = 1$.

Then, at low T, by a variable change $\gamma \equiv (E - E_{Fn(Fp)})/(k_B T)$, one has:

$$G_p(E_{Fn(Fp)}) \equiv 1 + E_{Fn(Fp)}^{-p} \times \int_{-\infty}^{\infty} \frac{e^\gamma}{(1+e^\gamma)^2} \times (k_B T \gamma + E_{Fn(Fp)})^p d\gamma = 1 + \sum_{\mu=1,2,\dots}^p C_p^\beta \times (k_B T)^\beta \times E_{Fn(Fp)}^{-\beta} \times I_\beta,$$

where $C_p^\beta \equiv p(p-1)\dots(p-\beta+1)/\beta!$ and the integral I_β is given by:

$$I_\beta = \int_{-\infty}^{\infty} \frac{\gamma^{\beta} \times e^\gamma}{(1+e^\gamma)^2} d\gamma = \int_{-\infty}^{\infty} \frac{\gamma^\beta}{(e^{\gamma/2} + e^{-\gamma/2})^2} d\gamma, \text{ vanishing for odd values of } \beta. \text{ Then, for even values}$$

of $\beta = 2n$, with $n=1, 2, \dots$, one obtains:

$$I_{2n} = 2 \int_0^{\infty} \frac{\gamma^{2n} \times e^\gamma}{(1+e^\gamma)^2} d\gamma.$$

Now, using an identity $(1 + e^\gamma)^{-2} \equiv \sum_{s=1}^{\infty} (-1)^{s+1} s \times e^{\gamma(s-1)}$, a variable change: $s\gamma = -t$, the Gamma function: $\int_0^{\infty} t^{2n} e^{-t} dt \equiv \Gamma(2n+1) = (2n)!$, and also the definition of the Riemann's zeta function: $\zeta(2n) \equiv 2^{2n-1} \pi^{2n} |B_{2n}| / (2n)!$, B_{2n} being the Bernoulli numbers, one finally gets: $I_{2n} = (2^{2n} - 2) \times \pi^{2n} \times |B_{2n}|$. So, from above Eq. of $\langle E^p \rangle_{FDDF}$, we get in the degenerate case the following ratio:

$$G_p(E_{Fn(Fp)}) \equiv \frac{\langle E^p \rangle_{FDDF}}{E_{Fn(Fp)}^p} = 1 + \sum_{n=1}^p \frac{p(p-1)\dots(p-2n+1)}{(2n)!} \times (2^{2n} - 2) \times |B_{2n}| \times y^{2n} \equiv G_{p \geq 1}(y), \quad (12)$$

$$\text{where } y \equiv \frac{\pi}{\xi_{n(0)}(N^*, T)} = \frac{\pi k_B T}{E_{Fn(Fp)}(N^*, T)}.$$

Then, some usual results of $G_{p \geq 1}(y)$ are given in Table 2 in Appendix 1, being needed to determine all the following electrical-and-thermoelectric properties.

ELECTRICAL-AND-THERMOELECTRIC PROPERTIES

Here, if denoting, for majority electrons (holes), the electrical conductivity by $\sigma(N, r_{d(a)}, x, T)$ expressed in $\text{ohm}^{-1} \times \text{cm}^{-1}$, the thermal conductivity by $\kappa(N, r_{d(a)}, x, T)$ in $\frac{\text{W}}{\text{cm} \times \text{K}}$, and the Lorenz number L defined by:

$L = \frac{\pi^2}{3} \times \left(\frac{k_B}{q}\right)^2 = 2.4429637 \left(\frac{W \times \text{ohm}}{K^2}\right) = 2.4429637 \times 10^{-8} (V^2 \times K^{-2})$, then the well-known Wiedemann-Frank law states that the ratio, $\frac{\kappa}{\sigma}$, is proportional to the temperature $T(K)$, as:

$$\frac{\kappa(N_r d_{(a)} x T)}{\sigma(N_r d_{(a)} x T)} = L \times T. \quad (13)$$

We now determine the general form of σ in the following.

First of all, it is expressed in terms of the kinetic energy of the electron (hole),

$$E_k \equiv \frac{\hbar^2 \times k^2}{2 \times m_{Cn(Cp)} \times m_e}, \text{ or the wave number } k, \text{ as:}$$

$$\sigma(k) \equiv \frac{q^2 \times k}{\pi \times \hbar} \times \frac{k}{k_{sn(sp)}} \times [k \times a_{Bn(Bp)}] \times \left(\frac{E_k}{\eta_{n(p)}}\right)^{1/2},$$

which is thus proportional to E_k^2 .

Then, for $E \geq 0$, we obtain: $\langle E^2 \rangle_{FDDF} \equiv G_2(y = \frac{\pi k_B T}{E_{Fn(Fp)}}) \times E_{Fn(Fp)}^2$, and $G_2(y) = \left(1 + \frac{y^2}{3}\right) \equiv G_2(N, r_{d(a)}, x, T)$, with $y \equiv \frac{\pi}{\xi_{n(p)}}$, $\xi_{n(p)} = \xi_{n(p)}(N, r_{d(a)}, x, T)$ for a presentation simplicity. Therefore, one obtains^[1]:

$$\begin{aligned} \sigma(N, r_{d(a)}, x, T) &\equiv \left[\frac{q^2}{\pi \times \hbar} \times \frac{k_{Fn(Fp)}(N^*)}{R_{sn(sp)}(N^*)} \times [k_{Fn(Fp)}(N^*) \times a_{Bn(Bp)}(r_{d(a)})] \times \sqrt{A_{n(p)}(N^*)} \right] \times \left[G_2(N, r_{d(a)}, x, T) \times \left(\frac{E_{Fn(Fp)}(N, r_{d(a)}, x, T)}{E_{Fn(Fpo)}(N^*)} \right)^2 \right] \left(\frac{1}{\text{ohm} \times \text{cm}} \right) \\ &= \frac{q^2}{\pi \times \hbar} = 7.7480735 \times 10^{-5} \text{ ohm}^{-1}, A_{n(p)}(N^*) = \frac{E_{Fn(Fpo)}(N^*)}{\eta_{n(p)}(N^*)}, R_{sn(sp)}(N^*) \equiv \frac{k_{sn(sp)}}{k_{Fn(Fp)}}, \end{aligned} \quad (14)$$

Which can be used to define the resistivity as: $\rho(N, r_{d(a)}, x, T) \equiv 1/\sigma(N, r_{d(a)}, x, T)$, noting again that $N^* \equiv N - N_{CDn(NDp)}(r_{d(a)}, x)$. This $\sigma(N, r_{d(a)}, x, T)$ -result is an essential one in this paper, being used to determine other electrical-and-thermoelectric properties.

In Eq. (14), one notes that at $T= 0$ K, $\sigma(N, r_{d(a)}, x, T = 0K)$ is proportional to $E_{Fn(Fpo)}^2$, or to $(N^*)^{\frac{4}{3}}$. Thus, $\sigma(N = N_{CDn(NDp)}, r_{d(a)}, x, T = 0K) = 0$ at $N^* = 0$, at which the metal-insulator transition (MIT) occurs.

Electrical Coefficients

The relaxation time τ is related to σ by^[1]:

$$\tau(N, r_{d(a)}, x, T) \equiv \sigma(N, r_{d(a)}, x, T) \times \frac{m_e(v)(x) \times m_a}{q^2 \times N^*}. \text{ Therefore, the mobility } \mu \text{ is given by:}$$

$$\mu(N, r_{d(a)}, x, T) \equiv \mu(N^*, r_{d(a)}, T) = \frac{q \times \tau(N, r_{d(a)}, x, T)}{m_c(y)(x) \times m_0} = \frac{\sigma(N, r_{d(a)}, x, T)}{q \times N^*} (\frac{cm^2}{V \times s}). \quad (15)$$

Here, at $T=0K$, $\mu(N^*, r_{d(a)}, T)$ is thus proportional to $(N^*)^{1/3}$, since $\sigma(N^*, r_{d(a)}, T=0K)$ is proportional to $(N^*)^{4/3}$. Thus, $\mu(N^* = 0, r_{d(a)}, T = 0K) = 0$ at $N^* = 0$, at which the metal-insulator transition (MIT) occurs.

Then, since τ and σ are both proportional to $E_{Fn(Fp)}(N^*, T)^2$, as given above, the Hall factor is defined by:

$r_H(N, r_{d(a)}, x, T) \equiv \frac{(\tau^2)_{FDDF}}{[(\tau)_{FDDF}]^2} = \frac{G_4(y)}{[G_2(y)]^2}$, $y \equiv \frac{\pi}{\xi_{n(p)}(N, r_{d(a)}, x, T)} = \frac{\pi k_B T}{E_{Fn(Fp)}(N, r_{d(a)}, x, T)}$, and therefore, the Hall mobility yields:

$$\mu_H(N, r_{d(a)}, x, T) \equiv \mu(N, r_{d(a)}, x, T) \times r_H(N^*, T) (\frac{cm^2}{V \times s}), \quad (16)$$

noting that, at $T=0K$, since $r_H(N, r_{d(a)}, x, T) = 1$, one then gets: $\mu_H(N, r_{d(a)}, x, T) \equiv \mu(N, r_{d(a)}, x, T)$.

Our generalized Einstein relation

Our generalized Einstein relation is found to be defined as [1]:

$$\frac{D(N, r_{d(a)}, x, T)}{\mu(N, r_{d(a)}, x, T)} \equiv \frac{N^*}{q} \times \frac{dE_{Fn(Fp)}}{dN^*} \equiv \frac{k_B \times T}{q} \times \left(u \frac{d\xi_{n(p)}(u)}{du} \right) = \sqrt{\frac{3 \times 1}{\pi^2}} \times T \times \left(u \frac{d\xi_{n(p)}(u)}{du} \right), \frac{k_B}{q} = \sqrt{\frac{3 \times 1}{\pi^2}} \quad (17)$$

where $D(N, r_{d(a)}, x, T)$ is the diffusion coefficient, $\xi_{n(p)}(u)$ is defined in Eq. (11), and the mobility $\mu(N, r_{d(a)}, x, T)$ is determined in Eq. (15). Then, by differentiating this function $\xi_{n(p)}(u)$ with respect to u , one thus obtains $\frac{d\xi_{n(p)}(u)}{du}$. Therefore, Eq. (17) can also be rewritten as:

$$\frac{D(N, r_{d(a)}, x, T)}{\mu(N, r_{d(a)}, x, T)} = \frac{k_B \times T}{q} \times u \frac{V'(u) \times W(u) - V(u) \times W'(u)}{W^2(u)},$$

where

$$W'(u) = ABu^{B-1} \quad \text{and}$$

$V'(u) = u^{-1} + 2^{-\frac{s}{2}} e^{-du} (1 - du) + \frac{2}{s} A u^{B-1} F(u) \left[\left(1 + \frac{sB}{2} \right) + \frac{4}{s} \times \frac{bu^{-\frac{4}{s}+2cu^{-\frac{s}{2}}}}{1+bu^{-\frac{4}{s}+2cu^{-\frac{s}{2}}}} \right]$. One remarks that: (i) as $u \rightarrow 0$, one has: $W^2 \approx 1$ and $u[V' \times W - V \times W'] \approx 1$, and therefore: $\frac{D_{n(p)}(u)}{\mu} \approx \frac{k_B \times T}{q}$, and (ii) as $u \rightarrow \infty$, one has: $W^2 \approx A^2 u^{2B}$ and $u[V' \times W - V \times W'] \approx \frac{2}{s} au^{2/3} A^2 u^{2B}$, and therefore, in this **highly degenerate case** and at $T=0K$, the **above generalized Einstein relation** is reduced to

the usual Einstein one: $\frac{D(N, r_d(a), x, T=0 K)}{\mu(N, r_d(a), x, T=0 K)} \approx \frac{2}{3} E_{Fn(Fpo)}(N^*)/q$. In other words, Eq. (17) verifies the correct limiting conditions.

Furthermore, in the present degenerate case ($u \gg 1$), Eq. (17) gives:

$$\frac{D(N, r_d(a), x, T)}{\mu(N, r_d(a), x, T)} \approx \frac{2}{3} \times \frac{E_{Fn(Fpo)}(u)}{q} \times \left[1 + \frac{4}{3} \times \frac{\left(bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}} \right)}{\left(1 + bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}} \right)} \right], \quad (18)$$

where $a = [3\sqrt{\pi}/4]^{2/3}$, $b = \frac{1}{8}(\frac{\pi}{a})^2$ and $c = \frac{62.3739855}{1920}(\frac{\pi}{a})^4$.

In Tables 3n(3p) given in Appendix 1, for given x , $N > N_{CDn}$ and $T(=4.2 \text{ K and } 77 \text{ K})$, and from Equations (14, 15, 16, 17), the numerical results of the coefficients: σ, μ, μ_H and D are found to be decreased with increasing $r_d(a)$, respectively.

Thermoelectric Coefficients

First of all, from Eq. (14), obtained for $\sigma(N, r_d(a), x, T)$, the well-known Mott definition for the thermoelectric power or for the Seebeck coefficient, S, is found to be given by:

$$S(N, r_d(a), x, T) \equiv \frac{-\pi^2}{3} \times \frac{k_B}{q > 0} \times k_B T \times \left[\frac{\partial \ln \sigma(E)}{\partial E} \right]_{E=E_{Fn(Fp)}} = \frac{-\pi^2}{3} \times \frac{k_B}{q} \times \frac{\partial \ln \sigma(\xi_{n(p)})}{\partial \xi_{n(p)}}.$$

Then, using Eq. (11), for the degenerate case, $\xi_{n(p)} \geq 0$, one gets, by putting

$$F_S(N, r_d(a), x, T) \equiv \left[1 - \frac{y^2}{3 \times G_2(y=\frac{\pi}{\xi_{n(p)}})} \right],$$

$$S(N, r_d(a), x, T) \equiv \frac{-\pi^2}{3} \times \frac{k_B}{q} \times \frac{2F_{Sb}(N^*, T)}{\xi_{n(p)}} = -\sqrt{\frac{3 \times L}{\pi^2}} \times \frac{2 \times \xi_{n(p)}}{\left(1 + \frac{3 \times \xi_{n(p)}^2}{\pi^2} \right)} = -2\sqrt{L} \times \frac{\sqrt{(ZT)_{Mott}}}{1 + (ZT)_{Mott}} \left(\frac{V}{K} \right) < 0, \quad (ZT)_{Mott} = \frac{\pi^2}{3 \times \xi_{n(p)}^2}, \quad (19)$$

according to:

$$\frac{\partial S}{\partial \xi_{n(p)}} = \sqrt{\frac{3 \times L}{\pi^2}} \times 2 \times \frac{\frac{3 \times \xi_{n(p)}^2}{\pi^2} - 1}{\left(1 + \frac{3 \times \xi_{n(p)}^2}{\pi^2} \right)^2} = \sqrt{\frac{3 \times L}{\pi^2}} \times 2 \times \frac{(ZT)_{Mott} \times [1 - (ZT)_{Mott}]}{[1 + (ZT)_{Mott}]^2}.$$

Here, one notes that: (i) as $\xi_{n(p)} \rightarrow +\infty$ or $\xi_{n(p)} \rightarrow +0$, one has a same limiting value of S:

$S \rightarrow -0$, (ii) at $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}} \simeq 1.8138$, since $\frac{\partial S}{\partial \xi_{n(p)}} = 0$, one therefore gets: a minimum

$(S)_{\min.} = -\sqrt{L} \approx -1.563 \times 10^{-4} \left(\frac{V}{K}\right)$, and (iii) at $\xi_{n(p)} = 1$ one obtains:
 $S \approx -1.322 \times 10^{-4} \left(\frac{V}{K}\right)$.

Further, the figure of merit, ZT, is found to be defined by:

$$ZT(N, r_{d(a)}, x, T) \equiv \frac{S^2 \times \sigma \times T}{\kappa} = \frac{S^2}{L} = \frac{4 \times (ZT)_{Mott}}{[1 + (ZT)_{Mott}]^2}. \quad (20)$$

Here, one notes that: (i) $\frac{\partial(ZT)}{\partial \xi_{n(p)}} = 2 \times \frac{S}{L} \times \frac{\partial S}{\partial \xi_{n(p)}} < 0$, (ii) at $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}} \approx 1.8138$, since $\frac{\partial(ZT)}{\partial \xi_{n(p)}} = 0$, one gets: a maximum $(ZT)_{max} = 1$, and $(ZT)_{Mott} = 1$, and (iii) at $\xi_{n(p)} = 1$, one obtains: $ZT \approx 0.715$ and $(ZT)_{Mott} = \frac{\pi^2}{3} \approx 3.290$.

Finally, the first Van-Cong coefficient, VC1, can be defined by:

$$VC1(N, r_{d(a)}, x, T) \equiv -N^* \times \frac{dS}{dN^*} \left(\frac{V}{K}\right) = N^* \times \frac{\partial S}{\partial \xi_{n(p)}} \times -\frac{\partial \xi_{n(p)}}{\partial N^*}, \text{ being equal to 0 for } \xi_{n(p)} = \sqrt{\frac{\pi^2}{3}}, \quad (21)$$

and the second Van-Cong coefficient, VC2, as:

$$VC2(N, r_{d(a)}, x, T) \equiv T \times VC1(V), \quad (22)$$

the Thomson coefficient, Ts, by:

$$Ts(N, r_{d(a)}, x, T) \equiv T \times \frac{dS}{dT} \left(\frac{V}{K}\right) = T \times \frac{\partial S}{\partial \xi_{n(p)}} \times \frac{\partial \xi_{n(p)}}{\partial T}, \text{ being equal to 0 for } \xi_{n(p)} = \sqrt{\frac{\pi^2}{3}}, \quad (23)$$

and the Peltier coefficient, Pt, as:

$$Pt(N, r_{d(a)}, x, T) \equiv T \times S(V). \quad (24)$$

One notes here that in next Tables 5n(p) and 6n(p) given in Appendix 1, obtained with such given physical conditions N(or T) for the decreasing $\xi_{n(p)}$, since $VC1(N, r_{d(a)}, x, T)$ and $Ts(N, r_{d(a)}, x, T)$ are expressed in terms of $\frac{-dS}{dN^*}$ and $\frac{dS}{dT}$, one has: $[VC1, Ts] < 0$ for $\xi_{n(p)} > \sqrt{\frac{\pi^2}{3}}$, $[VC1, Ts] = 0$ for $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}}$, and $[VC1, Ts] > 0$ for $\xi_{n(p)} < \sqrt{\frac{\pi^2}{3}}$, stating also that for $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}}$:

- (i) S, determined in Eq. (19), thus presents a same minimum
 $(S)_{\min.} = -\sqrt{L} \approx -1.563 \times 10^{-4} \left(\frac{V}{K}\right)$,

(ii) ZT, determined in Eq. (20), therefore presents **a same maximum:** $(ZT)_{max} = 1$, since the variations of ZT are expressed in terms of $[VC1, Ts] \times S, S < 0$.

Furthermore, it is interesting to remark that the (VC2)-coefficient is related to our generalized Einstein relation (17) by:

$$\frac{k_B}{q} \times VC2(N, r_d(a), x, T) \equiv -\frac{\partial S}{\partial \xi_n(\mu)} \times \frac{D(N, r_d(a), x, T)}{\mu(N, r_d(a), x, T)} \left(\frac{V^2}{K} \right), \frac{k_B}{q} = \sqrt{\frac{3 \times L}{\pi^2}}, \quad (25)$$

according, in this work, with the use of our Eq. (21), to:

$$VC2(N, r_d(a), x, T) \equiv -\frac{D(N, r_d(a), x, T)}{\mu(N, r_d(a), x, T)} \times 2 \times \frac{(ZT)_{Mott} \times [1 - (ZT)_{Mott}]}{[1 + (ZT)_{Mott}]^2} (V).$$

Of course, our relation (25) is reduced to: $\frac{D}{\mu}$, VC1 and VC2, being determined respectively by Equations (17, 21, 22).

Now, in the degenerate n(p)-type $X(x)$ – alloy, and for $N > N_{CDn(CDp)}$, and for $T=3K$ (80K), the numerical results of various thermoelectric coefficients are reported in Tables 4n(4p) in Appendix 1, noting that their variations with increasing $r_d(a)$ are represented by the arrows: ↗ (increase), and ↘ (decrease), respectively.

Then, in Tables 5n(5p) given Appendix 1 for a given N and with increasing T , and in Tables 6n(6p) given Appendix 1 for a given T and with decreasing N , the reduced Fermi-energy $\xi_{n(p)}$ decreases, and various thermoelectric coefficients are in variations, as indicated by the arrows as: (increase: ↗, decrease: ↘).

CONCLUDING REMARKS

Here, some concluding remarks can be given as follows.

(1) In the $n^+(p^+) - p(n)$ $X(x) \equiv GaAs_{1-x}Sb_x$ - crystalline alloy, $0 \leq x \leq 1$, the electrical-and-thermoelectric laws, relations, and various coefficients are found to be enhanced by our static dielectric constant law, $\epsilon(r_d(a), x)$, being, for a given x , decreased with increasing $r_d(a)$, as given in Equations (1a, 1b) and also given in Table 5 of our recent work^[2], by our accurate Fermi energy, $E_{Fn(Fp)}$, given in Eq. (11), and in particular by our electrical conductivity model given in Eq. (14).

(2) The generalized Mott criterium in the MIT is expressed in Equations (3, 5, 6), stating that the critical impurity density $N_{CDn(CDp)}$ is just the density of electrons (holes), localized in the

exponential conduction (valence)-band tail, $N_{CDn(CDp)}^{EBT}$, obtained with a precision of the order of 2.9×10^{-7} , as given in our previous work^[2], and the effective electron (hole)-density can be defined by: $N^* \equiv N - N_{CDn(CDp)} \simeq N - N_{CDn(CDp)}^{EBT}$, as that observed in the compensated crystals.

(3) The ratio of the inverse effective screening length $k_{sn(sp)}$ to Fermi wave number $k_{Fn(kp)}$ at 0 K, $R_{sn(sp)}(N^*)$, defined in Eq. (7), is valid for any density N^* .

(4) In Tables 5n(5p) given Appendix 1, for a given impurity density N and with increasing temperature T , and then in Tables 6n(6p) given Appendix 1, for a given T and with decreasing N , the reduced Fermi-energy $\xi_{n(p)}$ decreases, and other thermoelectric coefficients are in variations, as indicated by the arrows by: (increase: ↗, decrease: ↘). One remarks in these Tables that, for any given x , $r_{d(a)}$ and N (or T), with increasing T (or decreasing N), one obtains: (i) for $\xi_{n(p)} \simeq 1.8138$, while the numerical results of the Seebeck coefficient S present a **same minimum** $(S)_{min} = -\sqrt{L} \simeq -1.563 \times 10^{-4} \left(\frac{V}{K}\right)$, those of the figure of merit ZT show a **same maximum** $(ZT)_{max} = 1$, (ii) for $\xi_{n(p)} = 1$, the numerical results of S , ZT, the Mott figure of merit $(ZT)_{Mott}$, the Van-Cong coefficient VC1, and the Thomson coefficient Ts , present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715 , 3.290 , $1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$, respectively, and finally (iii) for $\xi_n \simeq 1.8138$, $(ZT)_{Mott} = 1$. It seems that these same results could represent a new law given for the thermoelectric properties, obtained in the degenerate case.

(5) Finally, our electrical-and-thermoelectric relation is given in Eq. (25) by:

$$\frac{k_B}{q} \times VC2(N, r_{d(a)}, x, T) \equiv -\frac{\partial S}{\partial \xi_{n(v)}} \times \frac{D(N, r_{d(a)}, x, T)}{\mu(N, r_{d(a)}, x, T)} \left(\frac{V^2}{K}\right), \quad \frac{k_B}{q} = \sqrt{\frac{3 \times L}{\pi^2}}, \text{ according, in this work, to:}$$

$$VC2(N, r_{d(a)}, x, T) \equiv -\frac{D(N, r_{d(a)}, x, T)}{\mu(N, r_{d(a)}, x, T)} \times 2 \times \frac{(ZT)_{Mott} \times [1 - (ZT)_{Mott}]}{[1 + (ZT)_{Mott}]^2} (V), \text{ being reduced to: } \frac{D}{\mu}, \text{ VC1 and}$$

VC2, determined respectively in Equations (17, 21, 22). This should be a new result.

REFERENCES

1. Van Cong, H. Electrical-and-Thermoelectric Laws, Relations, and Coefficients in n(p)-type Degenerate GaP(1-x)As(x)-Crystalline Alloy, Enhanced by Our Static Dielectric Constant Law and Electrical Conductivity (VI). WJERT, 2025; 11(3): 184-215.

2. Van Cong, H. New Critical Impurity Density in Metal-Insulator Transition, obtained in various n(p)-Type Degenerate Crystalline Alloys, being just That of Carriers Localized in Exponential Band Tails. WJERT, 2024; 10(4): 05-23.
3. Van Cong, H. Effects of donor size and heavy doping on optical, electrical and thermoelectric properties of various degenerate donor-silicon systems at low temperatures. American Journal of Modern Physics, 2018; 7(4): 136-165.
4. Van Cong, H. et al. Size effect on different impurity levels in semiconductors. Solid State Communications, 1984; 49: 697-699.
5. Van Cong, H. Diffusion coefficient in degenerate semiconductors. Phys. Stat. Sol. (b), 1984; 101: K27.
6. Van Cong, H. Same Maximal Figure of Merit $ZT=1$, Due to the Effect of Impurity Size, Obtained in the n(p)-Type Degenerate GaAs-Crystal ($\xi_{n(p)} \geq 1$), at Same Reduced Fermi Energy $\xi_{n(p)} (= 1.8138)$ and Same Minimum Seebeck Coefficient $S (= -1.563 \times 10^{-4} \frac{V}{K})$, at which Same $(ZT)_{Mott} \left(= \frac{\pi^2}{3\xi_{n(p)}^2} = 1 \right)$. SCIREA Journal of Physics, 2023; 8(2): 133-156.
7. Kim, H. S. et al. Characterization of Lorenz number with Seebeck coefficient measurement. APL Materials, 2015; 3(4): 041506.
8. Hyun, B. D. et al. Electrical-and-Thermoelectric Properties of $90\% Bi_2Te_3 - 5\% Sb_2Te_3 - 5\% Sb_2Se_3$ Single Crystals Doped with SbI_3 . Scripta Materialia, 1998; 40(1): 49-56.
9. Van Cong, H. and Debiais, G. A simple accurate expression of the reduced Fermi energy for any reduced carrier density. J. Appl. Phys., 1993; 73: 1545-1546.
10. Van Cong, H. and Doan Khanh, B. Simple accurate general expression of the Fermi-Dirac integral $F_j(a)$ and for $j > -1$. Solid-State Electron., 1992; 35(7): 949-951.
11. Van Cong, H. New series representation of Fermi-Dirac integral $F_j(-\infty < a < \infty)$ for arbitrary $j > -1$, and its effect on $F_j(a \geq 0_+)$ for integer $j \geq 0$. Solid-State Electron., 1991; 34(5): 489-492.

APPENDIX 1: Tables

Table 1: The values of energy-band-structure parameters are given in the following.

In the $\text{X}(x) \equiv \text{GaAs}_{1-x}\text{Sb}_x$ -crystalline alloy, in which $r_{\text{do}(ao)} = r_{\text{As(Ga)}} = 0.118$ nm (0.126 nm), we have: $g_{c(v)}(x) = 1 \times x + 1 \times (1 - x)$, $m_{c(v)}(x)/m_0 = 0.047$ (0.3) $\times x + 0.066$ (0.291) $\times (1 - x)$, $\epsilon_0(x) = 15.69 \times x + 13.13 \times (1 - x)$, $E_{go}(x) = 0.81 \times x + 1.52 \times (1 - x)$.

Table 2: Expressions for $G_{p=1}(y \equiv \frac{\pi}{\xi_{n(p)}})$, due to the Fermi-Dirac distribution function, noting that $G_{p=1}(y \equiv \frac{\pi k_B T}{E_{Fn(Fp)}} = \frac{\pi}{\xi_{n(p)}}) = 1$, used to determine the electrical-and-thermoelectric coefficients.

$G_{3/2}(y)$	$G_2(y)$	$G_{5/2}(y)$	$G_3(y)$	$G_{7/2}(y)$	$G_4(y)$	$G_{9/2}(y)$
$(1 + \frac{y^2}{8} + \frac{7y^4}{640})$	$(1 + \frac{y^2}{3})$	$(1 + \frac{5y^2}{8} - \frac{7y^4}{384})$	$(1 + y^2)$	$(1 + \frac{35y^2}{24} + \frac{49y^4}{384})$	$(1 + 2y^2 + \frac{7y^4}{15})$	$(1 + \frac{21y^2}{8} + \frac{147y^4}{128})$

Table 3n: Here, one notes that, for given x , $N > N_{CDn}$ and $T(=4.2$ K and 77 K), the functions: σ, μ, μ_H, D , expressed respectively in $(\frac{10^8}{\text{ohm} \times \text{cm}}, \frac{10^8 \times \text{cm}^2}{\text{V} \times \text{s}}, \frac{10^8 \times \text{cm}^2}{\text{V} \times \text{s}}, \frac{10^2 \times \text{cm}^2}{\text{s}})$, decrease with increasing r_d .

Donor r_d (nm)	P	As	Sb	Sn
0.110		0.118	0.136	0.140

For $x=0$, the values of (σ, μ, μ_H, D) at 4.2K

N (10^{18} cm^{-3})				
3	1.23, 2.566, 2.566, 1.96	1.19, 2.499, 2.499, 1.91	1.05, 2.189, 2.190, 1.67	0.98, 2.062, 2.063, 1.57
10	3.10, 1.936, 1.936, 3.30	3.01, 1.884, 1.884, 3.22	2.64, 1.648, 1.648, 2.81	2.48, 1.553, 1.553, 2.65
40	9.34, 1.458, 1.458, 6.28	9.07, 1.415, 1.415, 6.09	7.83, 1.223, 1.223, 5.27	7.34, 1.147, 1.147, 4.94
70	14.8, 1.324, 1.324, 8.28	14.4, 1.284, 1.284, 8.03	12.4, 1.103, 1.013, 6.90	11.6, 1.031, 1.031, 6.45

For $x=0.5$, the values of (σ, μ, μ_H, D) at 4.2K

N (10^{18} cm^{-3})				
3	1.36, 2.847, 2.847, 2.54	1.33, 2.773, 2.773, 2.48	1.16, 2.428, 2.428, 2.17	1.09, 2.286, 2.286, 2.04
10	3.44, 2.147, 2.147, 4.28	3.35, 2.090, 2.090, 4.17	2.93, 1.829, 1.829, 3.65	2.76, 1.724, 1.724, 3.44
40	10.3, 1.612, 1.612, 8.11	10.0, 1.565, 1.565, 7.87	8.67, 1.354, 1.354, 6.81	8.13, 1.270, 1.270, 6.39
70	16.4, 1.462, 1.462, 10.7	15.9, 1.418, 1.418, 10.3	13.7, 1.219, 1.219, 8.91	12.8, 1.140, 1.140, 8.33

For $x=1$, the values of (σ, μ, μ_H, D) at 4.2K

N (10^{18} cm^{-3})				
3	1.54, 3.204, 3.204, 3.44	1.50, 3.120, 3.121, 3.35	1.31, 2.731, 2.732, 2.93	1.23, 2.571, 2.571, 2.76
10	3.87, 2.416, 2.416, 5.80	3.77, 3.352, 3.352, 5.64	3.30, 2.059, 2.059, 4.94	3.11, 1.940, 1.940, 4.66
40	11.6, 1.810, 1.810, 10.9	11.3, 1.757, 1.757, 10.6	9.74, 1.521, 1.521, 9.20	9.14, 1.426, 1.426, 8.63
70	18.4, 1.639, 1.639, 14.4	17.8, 1.590, 1.590, 14.0	15.3, 1.368, 1.368, 12.0	14.3, 1.280, 1.280, 11.2

For $x=0$, the values of (σ, μ, μ_H, D) at 77 K

N (10^{18} cm^{-3})				
3	1.25, 2.615, 2.728, 1.99	1.22, 2.547, 2.657, 1.94	1.07, 2.232, 2.329, 1.69	1.00, 2.102, 2.193, 1.60
10	3.11, 1.943, 1.960, 3.31	3.03, 1.891, 1.908, 3.23	2.65, 1.655, 1.669, 2.82	2.49, 1.559, 1.573, 2.66
40	9.35, 1.459, 1.461, 6.28	9.07, 1.416, 1.418, 6.10	7.84, 1.224, 1.225, 5.27	7.35, 1.147, 1.149, 4.94
70	14.8, 1.324, 1.325, 8.28	14.4, 1.284, 1.285, 8.03	12.4, 1.103, 1.014, 6.90	11.6, 1.031, 1.032, 6.45

For $x=0.5$, the values of (σ, μ, μ_H, D) at 77 K

N (10^{18} cm^{-3})				
3	1.38, 2.887, 2.979, 2.57	1.35, 2.812, 2.901, 2.50	1.18, 2.462, 2.541, 2.19	1.11, 2.319, 2.392, 2.06

10	3.45, 2.153, 2.167, 4.29	3.36, 2.096, 2.110, 4.18	2.94, 1.834, 1.843, 3.66	2.77, 1.729, 1.740, 3.45
40	10.3, 1.613, 1.615, 8.11	10.0, 1.566, 1.568, 7.88	8.68, 1.354, 1.356, 6.81	8.14, 1.270, 1.271, 6.39
70	16.4, 1.462, 1.463, 10.7	15.9, 1.418, 1.419, 10.4	13.7, 1.219, 1.220, 8.91	12.8, 1.140, 1.141, 8.33

For $x=1$, the values of (σ, μ, μ_H, D) at 77 K

$N (10^{19} \text{ cm}^{-3})$				
3	1.55, 3.235, 3.307, 3.47	1.51, 3.151, 3.220, 3.38	1.32, 2.758, 2.819, 2.96	1.25, 2.596, 2.654, 2.78
10	3.88, 2.421, 2.431, 5.81	3.77, 2.356, 2.367, 5.65	3.30, 2.063, 2.072, 4.95	3.11, 1.944, 1.953, 4.66
40	11.6, 1.810, 1.811, 10.9	11.3, 1.758, 1.759, 10.6	9.75, 1.521, 1.522, 9.20	9.14, 1.427, 1.428, 8.63
70	18.4, 1.639, 1.640, 14.4	17.8, 1.590, 1.590, 14.0	15.3, 1.368, 1.368, 12.0	14.3, 1.280, 1.280, 11.2

Table 3p: Here, one notes that, for given x , $N > N_{CDP}$ and $T(=4.2 \text{ K} \text{ and } 77 \text{ K})$, the functions: σ, μ, μ_H, D , expressed respectively in $\left(\frac{10^3}{\text{ohm} \times \text{cm}}, \frac{10^2 \times \text{cm}^2}{\text{V} \times \text{s}}, \frac{10^2 \times \text{cm}^2}{\text{V} \times \text{s}}, \frac{10 \times \text{cm}^2}{\text{s}} \right)$, decrease with increasing r_a .

Acceptor	Ga	Mg	In	Cd
r_a (nm)	0.126	0.140	0.144	0.148

For $x=0$, the values of (σ, μ, μ_H, D) at 4.2K

$N (10^{19} \text{ cm}^{-3})$				
3	4.50, 9.743, 9.744, 7.65	4.12, 8.973, 8.974, 7.02	3.89, 8.531, 8.532, 6.65	3.65, 8.040, 8.040, 6.24
5	7.03, 8.982, 8.982, 10.0	6.43, 8.244, 8.245, 9.18	6.08, 7.821, 7.821, 8.69	5.69, 7.351, 7.351, 8.14
8	10.6, 8.404, 8.404, 12.9	9.69, 7.693, 7.693, 11.8	9.16, 7.285, 7.286, 11.1	8.57, 6.833, 6.833, 10.4
10	12.9, 8.162, 8.162, 14.6	11.8, 7.464, 7.464, 13.3	11.1, 7.063, 7.063, 12.6	10.4, 6.618, 6.618, 11.8

For $x=0.5$, the values of (σ, μ, μ_H, D) at 4.2K

$N (10^{19} \text{ cm}^{-3})$				
3	5.10, 10.95, 10.95, 8.52	4.67, 10.07, 10.07, 7.80	4.41, 9.564, 9.566, 7.39	4.13, 9.002, 9.003, 6.93
5	7.98, 10.14, 10.14, 11.2	7.29, 9.296, 9.297, 10.2	6.89, 8.811, 8.812, 9.68	6.45, 8.272, 8.273, 9.07
8	12.1, 9.522, 9.522, 14.4	11.0, 8.707, 8.707, 13.2	10.4, 8.239, 8.239, 12.4	9.73, 7.720, 7.720, 11.6
10	14.7, 9.262, 9.262, 16.3	13.4, 8.460, 8.460, 14.9	12.7, 8.000, 8.001, 14.1	11.8, 7.490, 7.490, 13.1

For $x=1$, the values of (σ, μ, μ_H, D) at 4.2K

$N (10^{19} \text{ cm}^{-3})$				
3	5.72, 12.19, 12.19, 9.38	5.22, 11.19, 11.20, 8.59	4.94, 10.62, 10.62, 8.13	4.63, 9.988, 9.989, 7.62
5	8.94, 11.33, 11.33, 12.3	8.17, 10.37, 10.38, 11.3	7.72, 9.827, 9.827, 10.6	7.22, 9.217, 9.218, 9.99
8	13.5, 10.67, 10.67, 15.9	12.3, 9.748, 9.748, 14.5	11.7, 9.218, 9.218, 13.7	10.9, 8.630, 8.631, 12.9
10	16.5, 10.39, 10.39, 18.0	15.1, 9.484, 9.484, 16.4	14.2, 8.963, 8.963, 15.5	13.3, 8.385, 8.385, 14.5

For $x=0$, the values of (σ, μ, μ_H, D) at 77K

$N (10^{19} \text{ cm}^{-3})$				
3	4.59, 9.921, 10.33, 7.76	4.19, 9.139, 9.516, 7.12	3.97, 8.689, 9.050, 6.74	3.71, 8.191, 8.534, 6.33
5	7.09, 9.063, 9.248, 10.1	6.48, 8.319, 8.490, 9.24	6.13, 7.892, 8.055, 8.75	5.74, 7.418, 7.572, 8.20
8	10.7, 8.444, 8.535, 12.9	9.74, 7.730, 7.814, 11.8	9.21, 7.320, 7.400, 11.2	8.61, 6.866, 6.941, 10.5
10	13.0, 8.191, 8.257, 14.6	11.8, 7.490, 7.550, 13.3	11.2, 7.088, 7.145, 12.6	10.5, 6.642, 6.695, 11.8

For $x=0.5$, the values of (σ, μ, μ_H, D) at 77K

$N (10^{19} \text{ cm}^{-3})$				
3	5.20, 11.16, 11.62, 8.64	4.75, 10.26, 10.69, 7.92	4.50, 9.745, 10.16, 7.50	4.21, 9.173, 9.563, 7.04
5	8.05, 10.23, 10.45, 11.3	7.35, 9.383, 9.580, 10.3	6.95, 8.893, 9.081, 9.75	6.51, 8.350, 8.527, 9.13
8	12.1, 9.569, 9.675, 14.5	11.1, 8.749, 8.847, 13.2	10.4, 8.280, 8.372, 12.5	9.78, 7.758, 7.845, 11.7

10	14.7, 9.296, 9.373, 16.3	13.4, 8.491, 8.561, 14.9	12.7, 8.029, 8.096, 14.1	11.9, 7.517, 7.580, 13.2
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For $x=1$, the values of (σ, μ, μ_H, D) at 77K

$N (10^{19} \text{ cm}^{-3})$	3	5	8	10
	5.82, 12.42, 12.95, 9.52	5.33, 11.41, 11.90, 8.71	5.04, 10.83, 11.29, 8.25	4.72, 10.18, 10.62, 7.74
	9.03, 11.44, 11.68, 12.4	8.24, 10.47, 10.70, 11.4	7.79, 9.921, 10.13, 10.7	7.29, 9.305, 9.507, 10.1
	13.6, 10.72, 10.85, 16.0	12.4, 9.797, 9.909, 14.6	11.7, 9.265, 9.371, 13.8	11.0, 8.674, 8.774, 12.9
	16.6, 10.43, 10.52, 18.1	15.1, 9.520, 9.601, 16.5	14.3, 8.997, 9.073, 15.6	13.3, 8.416, 8.488, 14.6

Table 4n: In the lightly degenerate n-type $X(x)$ – alloy, in which $N=5 \times 10^{17} \text{ cm}^{-3}$, and for $T=3\text{K}$ and 80K , the numerical results of various thermoelectric coefficients are reported. Further, their variations with increasing $r_{d(a)}$ are represented by the arrows: \nearrow (increase), and \searrow (decrease).

Donor	P	As	Sb	Sn
For $x=0$, one has:				
$\xi_n(T=3\text{K})$	\searrow	132.351	132.207	131.342
$\xi_n(T=80\text{K})$	\searrow	5.206	5.200	5.168
$\kappa_{(T=3\text{K})} \left(\frac{10^{-5} \times W}{\text{cm}^2 \times K} \right)$	\searrow	2.165	2.098	1.791
$\kappa_{(T=80\text{K})} \left(\frac{10^{-4} \times W}{\text{cm}^2 \times K} \right)$	\searrow	7.120	6.905	5.906
$-S_{(T=3\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	4.283	4.288	4.316
$-S_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	9.713	9.720	9.767
$-VC1_{(T=3\text{K})} \left(\frac{10^{-6} \times V}{K} \right)$	\searrow	2.854	2.857	2.876
$-VC1_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	4.748	4.750	4.765
$-VC2_{(T=3\text{K})} \left(\frac{10^{-6} \times V}{K} \right)$	\searrow	8.562	8.571	8.628
$-VC2_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	3.798	3.800	3.812
$-Ts_{(T=3\text{K})} \left(\frac{10^{-6} \times V}{K} \right)$	\searrow	4.281	4.286	4.314
$-Ts_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	7.122	7.126	7.147
$-Pt_{(T=3\text{K})} (10^{-5} \times V)$	\searrow	1.285	1.286	1.295
$-Pt_{(T=80\text{K})} (10^{-3} \times V)$	\searrow	7.770	7.776	7.814
$ZT_{(T=3\text{K})} (10^{-4})$	\nearrow	7.510	7.526	7.625
$ZT_{(T=80\text{K})} (10^{-1})$	\nearrow	3.861	3.868	3.905

For $x=0.5$, one has:

Donor	P	As	Sb	Sn
For $x=0.5$, one has:				
$\xi_n(T=3\text{K})$	\searrow	155.991	155.912	155.435
$\xi_n(T=80\text{K})$	\searrow	6.067	6.064	6.046
$\kappa_{(T=3\text{K})} \left(\frac{10^{-5} \times W}{\text{cm}^2 \times K} \right)$	\searrow	2.420	2.347	2.011
$\kappa_{(T=80\text{K})} \left(\frac{10^{-4} \times W}{\text{cm}^2 \times K} \right)$	\searrow	7.560	7.334	6.288
$-S_{(T=3\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	3.634	3.636	3.647
$-S_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	8.579	8.582	8.603
$-VC1_{(T=3\text{K})} \left(\frac{10^{-6} \times V}{K} \right)$	\searrow	2.422	2.423	2.431
$-VC1_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	4.459	4.460	4.465
$-VC2_{(T=3\text{K})} \left(\frac{10^{-6} \times V}{K} \right)$	\searrow	7.266	7.269	7.292
$-VC2_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	3.567	3.568	3.572
$-Ts_{(T=3\text{K})} \left(\frac{10^{-6} \times V}{K} \right)$	\searrow	3.633	3.635	3.646
$-Ts_{(T=80\text{K})} \left(\frac{10^{-5} \times V}{K} \right)$	\searrow	6.689	6.690	6.702

$-Pt_{(T=3K)}(10^{-5} \times V)$	↗	1.090	1.091	1.094	1.096
$-Pt_{(T=80K)}(10^{-3} \times V)$	↘	6.863	6.866	6.882	6.892
$ZT_{(T=3K)}(10^{-4})$	↗	5.406	5.412	5.445	5.464
$ZT_{(T=80K)}(10^{-1})$	↗	3.013	3.015	3.030	3.038

For $x=1$, one has:

$\xi_n(T=3K)$	↘	188.351	188.309	188.054	187.912
$\xi_n(T=80K)$	↘	7.244	7.242	7.233	7.228
$\kappa_{(T=3K)}(\frac{10^{-5} \times W}{cm \times K})$	↘	2.730	2.648	2.272	2.119
$\kappa_{(T=80K)}(\frac{10^{-4} \times W}{cm \times K})$	↘	8.136	7.894	6.775	6.319
$-S_{(T=3K)}(\frac{10^{-5} \times V}{K})$	↘	3.010	3.011	3.015	3.017
$-S_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	7.365	7.367	7.375	7.380
$-VC1_{(T=3K)}(\frac{10^{-6} \times V}{K})$	↘	2.006	2.007	2.009	2.011
$-VC1_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	4.112	4.113	4.115	4.117
$-VC2_{(T=3K)}(\frac{10^{-6} \times V}{K})$	↘	6.018	6.020	6.028	6.032
$-VC2_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	3.289	3.290	3.292	3.293
$-Ts_{(T=3K)}(\frac{10^{-6} \times V}{K})$	↘	3.009	3.010	3.014	3.016
$-Ts_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	6.168	6.169	6.173	6.175
$-Pt_{(T=3K)}(10^{-5} \times V)$	↘	0.903	0.904	0.905	0.906
$-Pt_{(T=80K)}(10^{-3} \times V)$	↘	5.892	5.893	5.900	5.904
$ZT_{(T=3K)}(10^{-4})$	↗	3.709	3.710	3.720	3.726
$ZT_{(T=80K)}(10^{-1})$	↗	2.220	2.221	2.226	2.229

Table 4p: In the lightly degenerate p-type X(x) – alloy, in which $N=2 \times 10^{19} \text{ cm}^{-3}$, and for $T=3\text{K}$ and 80K , the numerical results of various thermoelectric coefficients are reported. Further, their variations with increasing $r_d(a)$ are represented by the arrows: ↗ (increase), and ↘ (decrease).

Acceptor		Ga	Mg	In	Cd
For $x=0$, one has:					
$\xi_n(T=3K)$	↘	343.331	340.811	339.015	336.619
$\xi_n(T=80K)$	↘	12.972	12.878	12.811	12.722
$\kappa_{(T=3K)}(\frac{10^{-5} \times W}{cm \times K})$	↘	23.190	21.191	20.030	18.726
$\kappa_{(T=80K)}(\frac{10^{-4} \times W}{cm \times K})$	↘	6.400	5.851	5.533	5.175
$-S_{(T=3K)}(\frac{10^{-5} \times V}{K})$	↘	1.651	1.664	1.672	1.684
$-S_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	4.287	4.317	4.339	4.368
$-VC1_{(T=3K)}(\frac{10^{-6} \times V}{K})$	↘	1.101	1.109	1.115	1.223
$-VC1_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	2.707	2.723	2.735	2.752
$-VC2_{(T=3K)}(\frac{10^{-6} \times V}{K})$	↘	3.302	3.327	3.344	3.368
$-VC2_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	2.165	2.179	2.188	2.201
$-Ts_{(T=3K)}(\frac{10^{-6} \times V}{K})$	↘	1.651	1.663	1.672	1.684
$-Ts_{(T=80K)}(\frac{10^{-5} \times V}{K})$	↘	4.060	4.085	4.103	4.128
$-Pt_{(T=3K)}(10^{-5} \times V)$	↘	0.495	0.499	0.502	0.505
$-Pt_{(T=80K)}(10^{-3} \times V)$	↘	3.430	3.454	3.471	3.494
$ZT_{(T=3K)}(10^{-4})$	↗	1.116	1.133	1.145	1.161

$ZT_{(T=80K)}(10^{-1})$	↗	0.752	0.763	0.770	0.781
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For $x=0.5$, one has:

$\xi_n(T=2K)$	↘	340.935	338.979	337.585	335.727
$\xi_n(T=80K)$	↘	12.883	12.810	12.758	12.689
$\kappa_{(T=2K)} \left(\frac{10^{-5} \times W}{cm \times K}\right)$	↘	26.289	24.035	22.730	21.267
$\kappa_{(T=80K)} \left(\frac{10^{-5} \times W}{cm \times K}\right)$	↘	7.259	6.639	6.280	5.878
$-S_{(T=2K)} \left(\frac{10^{-5} \times V}{K}\right)$	↘	1.663	1.673	1.679	1.689
$-S_{(T=80K)} \left(\frac{10^{-5} \times V}{K}\right)$	↘	4.316	4.339	4.356	4.379
$-VC1_{(T=2K)} \left(\frac{10^{-6} \times V}{K}\right)$	↘	1.108	1.115	1.119	1.126
$-VC1_{(T=80K)} \left(\frac{10^{-5} \times V}{K}\right)$	↘	2.723	2.736	2.745	2.758
$-VC2_{(T=2K)} \left(\frac{10^{-6} \times V}{K}\right)$	↘	3.326	3.345	3.359	3.377
$-VC2_{(T=80K)} \left(\frac{10^{-3} \times V}{K}\right)$	↘	2.178	2.189	2.196	2.206
$-TS_{(T=2K)} \left(\frac{10^{-6} \times V}{K}\right)$	↘	1.663	1.672	1.679	1.689
$-TS_{(T=80K)} \left(\frac{10^{-5} \times V}{K}\right)$	↘	4.084	4.104	4.118	4.137
$-Pt_{(T=2K)}(10^{-5} \times V)$	↘	0.499	0.502	0.504	0.507
$-Pt_{(T=80K)}(10^{-3} \times V)$	↘	3.452	3.471	3.485	3.503
$ZT_{(T=2K)}(10^{-4})$	↗	1.132	1.145	1.155	1.167
$ZT_{(T=80K)}(10^{-1})$	↗	0.762	0.771	0.777	0.785

For $x=1$, one has:

$\xi_n(T=2K)$	↘	337.828	336.271	335.162	333.685
$\xi_n(T=80K)$	↘	12.767	12.709	12.668	12.613
$\kappa_{(T=2K)} \left(\frac{10^{-5} \times W}{cm \times K}\right)$	↘	29.427	26.908	25.451	23.823
$\kappa_{(T=80K)} \left(\frac{10^{-5} \times W}{cm \times K}\right)$	↘	8.130	7.437	7.036	6.588
$-S_{(T=2K)} \left(\frac{10^{-6} \times V}{K}\right)$	↘	1.678	1.686	1.692	1.699
$-S_{(T=80K)} \left(\frac{10^{-5} \times V}{K}\right)$	↘	4.353	4.372	4.386	4.404
$-VC1_{(T=2K)} \left(\frac{10^{-6} \times V}{K}\right)$	↘	1.119	1.124	1.128	1.133
$-VC1_{(T=80K)} \left(\frac{10^{-5} \times V}{K}\right)$	↘	2.743	2.754	2.762	2.772
$-VC2_{(T=2K)} \left(\frac{10^{-6} \times V}{K}\right)$	↘	3.356	3.372	3.383	3.398
$-VC2_{(T=80K)} \left(\frac{10^{-3} \times V}{K}\right)$	↘	2.195	2.203	2.209	2.217
$-TS_{(T=2K)} \left(\frac{10^{-6} \times V}{K}\right)$	↘	1.678	1.686	1.691	1.699
$-TS_{(T=80K)} \left(\frac{10^{-5} \times V}{K}\right)$	↘	4.115	4.131	4.142	4.158
$-Pt_{(T=2K)}(10^{-5} \times V)$	↘	0.503	0.506	0.507	0.510
$-Pt_{(T=80K)}(10^{-3} \times V)$	↘	3.482	3.498	3.508	3.523
$ZT_{(T=2K)}(10^{-4})$	↗	1.153	1.164	1.171	1.182
$ZT_{(T=80K)}(10^{-1})$	↗	0.776	0.782	0.787	0.794

Table 5n: Here, for a given N and with increasing T , the reduced Fermi-energy ξ_n decreases, and other thermoelectric coefficients are in variations, as indicated by the arrows as: (increase: ↗, decrease: ↘). One notes here that with increasing T : (i) for $\xi_n \approx 1.8138$, while the numerical results of S present a same minimum (S)_{min} ($\approx -1.563 \times 10^{-4} \frac{V}{K}$), those of ZT show a same maximum (ZT)_{max} = 1, (ii) for $\xi_n = 1$, those of S , ZT , (ZT)_{Mott}, $VC1$, and TS present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$ respectively, and (iii) for $\xi_n \approx 1.8138$, (ZT)_{Mott} = 1.

For x=0,

In the degenerate P- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_p) = 2.507675 \times 10^{18} \text{ cm}^{-2}$, one gets:

T(K)	15.263	15.5943916	15.929	21.2202591	21.242
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-0.933	0	0.999	23.447	23.558
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-3}V)	-2.384	-2.437	-2.488	-2.8047	-2.8039

In the degenerate As- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_{As}) = 2.6660176 \times 10^{18} \text{ cm}^{-2}$, one gets:

T(K)	15.8977	16.244123	16.593	22.1043894	22.127
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-0.975	0	1.042	24.424	24.540
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-3}V)	-2.483	-2.539	-2.592	-2.9215	-2.9207

In the degenerate Sb- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_{Sb}) = 3.619757 \times 10^{18} \text{ cm}^{-2}$, one gets:

T(K)	19.493	19.917762	20.346	27.103339	27.13
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-1.195	0	1.279	29.948	30.084
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-3}V)	-3.045	-3.113	-3.178	-3.5822	-3.5813

In the degenerate Sn- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_{Sn}) = 4.152416 \times 10^{18} \text{ cm}^{-2}$, one gets:

T(K)	21.3612	21.8267041	22.296	29.700956	29.731
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-1.310	0	1.402	32.818	32.971
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-3}V)	-3.337	-3.411	-3.483	-3.9256	-3.9246

For x=0.5,

In the degenerate P- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_p) = 1.1901097 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	8471	11.083436	11.3219	15.081922	15.097
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-0.665	0	0.712	16.665	16.742
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt(10^{-3}V)	-1.694	-1.732	-1.768	-1.9934	-1.9929

In the degenerate As- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_{As}) = 1.2652571 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	11.299	11.5452212	11.7935	15.7103014	15.7264
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-0.693	0	0.742	17.359	17.441
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt(10^{-3}V)	-1.765	-1.804	-1.842	-2.0764	-2.0759

In the degenerate Sb- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_{Sb}) = 1.7178893 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	13.855	14.156195	14.460	19.263216	19.282
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-0.848	0	0.907	21.285	21.381
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt(10^{-3}V)	-2.164	-2.213	-2.259	-2.5460	-2.5454

In the degenerate Sn- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_{Sn}) = 1.9706824 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	15.183	15.5129421	15.846	21.109427	21.131
ξ_m	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-4} \frac{\text{V}}{\text{K}})$	-0.929	0	0.995	23.325	23.435
$T_s(10^{-4} \frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt(10^{-3}V)	-2.371	-2.425	-2.475	-2.7900	-2.7893

For x=1,

In the degenerate P- $\text{X}(\text{x})$ - alloy, for $N = 2 \times N_{\text{CDn}}(r_p) = 5.3071132 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	7.6111	7.7768892	7.944	10.5824972	10.593
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ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.466	0	0.499	11.693	11.747
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.189	-1.215	-1.241	-1.3987	-1.3983

In the degenerate As- $x(x)$ – alloy, for $N = 2 \times N_{CDn}(r_{As}) = 5.6422212 \times 10^{15} \text{ cm}^{-3}$, one gets:

T(K)	7.9282	8.100909	8.2749	11.023411	11.0347
ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.486	0	0.520	12.180	12.240
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.238	-1.266	-1.292	-1.4570	-1.4566

In the degenerate Sb- $x(x)$ – alloy, for $N = 2 \times N_{CDn}(r_{Sb}) = 7.6606658 \times 10^{15} \text{ cm}^{-3}$, one gets:

T(K)	9.722	9.9329446	10.146	13.5163763	13.53
ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.594	0	0.636	14.935	15.004
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.518	-1.552	-1.585	-1.7865	-1.7860

In the degenerate Sn- $x(x)$ – alloy, for $N = 2 \times N_{CDn}(r_{Sn}) = 8.7879582 \times 10^{15} \text{ cm}^{-3}$, one gets:

T(K)	10.6528	10.8849305	11.118	14.811803	14.827
ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.653	0	0.696	16.366	16.444
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.664	-1.701	-1.737	-1.9577	-1.9572

Table 5p: Here, for a given N and with increasing T , the reduced Fermi-energy ξ_p decreases, and other thermoelectric coefficients are in variations, as indicated by the arrows as: (increase: \nearrow , decrease: \searrow). One notes here that with increasing T : (i) for $\xi_p \approx 1.8138$, while the numerical results of S present a same minimum $(S)_{\min} (\approx -1.563 \times 10^{-4} \frac{V}{K})$, those of ZT show a same maximum $(ZT)_{\max} = 1$, (ii) for $\xi_p = 1$, those of S , ZT, $(ZT)_{Mott}$, VC1, and T_s present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-2} V$, respectively, and (iii) for $\xi_p \approx 1.8138$, $(ZT)_{Mott} = 1$.

For $x=0$,

In the degenerate Ga- $x(x)$ -alloy, for $N = 2 \times N_{Cd_p}(r_{Ga}) = 2.285126 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	\nearrow	70.095	71.621813	73.16	97.46026	97.56
ξ_p	\searrow	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$		-1.562	\searrow	-1.563 \nearrow	-1.562 \nearrow	-1.322 \nearrow
ZT		0.999	\nearrow	1 \searrow	0.998 \searrow	0.715 \searrow
$(ZT)_{Mott}$	\nearrow	0.931	1		1.074	3.290
$VC1 (10^{-4} \frac{V}{K})$		-0.061	\nearrow	0 \nearrow	0.063 \nearrow	1.105 \nearrow
$VC2 (10^{-2} \frac{V}{K})$		-0.043	\nearrow	0 \nearrow	0.046 \nearrow	1.077 \nearrow
$T_s (10^{-4} \frac{V}{K})$		-0.092	\nearrow	0 \nearrow	0.094 \nearrow	1.657 \nearrow
Pt ($10^{-2} V$)		-1.095	\searrow	-1.119 \searrow	-1.143 \searrow	-1.2881 \nearrow
						-1.2878 \nearrow

In the degenerate Mg- $x(x)$ -alloy, for $N = 2 \times N_{Cd_p}(r_{Mg}) = 2.6994914 \times 10^{18} \text{ cm}^{-3}$, one gets

T(K)	\nearrow	78.331	80.037437	81.759	108.911924	109.023
ξ_p	\searrow	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$		-1.562	\searrow	-1.563 \nearrow	-1.562 \nearrow	-1.322 \nearrow
ZT		0.999	\nearrow	1 \searrow	0.998 \searrow	0.715 \searrow
$(ZT)_{Mott}$	\nearrow	0.931	1		1.074	3.290
$VC1 (10^{-4} \frac{V}{K})$		-0.061	\nearrow	0 \nearrow	0.063 \nearrow	1.105 \nearrow
$VC2 (10^{-2} \frac{V}{K})$		-0.048	\nearrow	0 \nearrow	0.051 \nearrow	1.203 \nearrow
$T_s (10^{-4} \frac{V}{K})$		-0.092	\nearrow	0 \nearrow	0.094 \nearrow	1.657 \nearrow
Pt ($10^{-2} V$)		-1.223	\searrow	-1.251 \searrow	-1.277 \searrow	-1.4395 \nearrow
						-1.4391 \nearrow

In the degenerate In- $x(x)$ -alloy, for $N = 2 \times N_{Cd_p}(r_{In}) = 2.9940338 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	\nearrow	83.93	85.758335	87.6	116.696705	116.81
ξ_p	\searrow	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$		-1.562	\searrow	-1.563 \nearrow	-1.562 \nearrow	-1.322 \nearrow
ZT		0.999	\nearrow	1 \searrow	0.998 \searrow	0.715 \searrow
$(ZT)_{Mott}$	\nearrow	0.931	1		1.074	3.290
$VC1 (10^{-4} \frac{V}{K})$		-0.061	\nearrow	0 \nearrow	0.063 \nearrow	1.105 \nearrow
$VC2 (10^{-2} \frac{V}{K})$		-0.051	\nearrow	0 \nearrow	0.055 \nearrow	1.289 \nearrow
$T_s (10^{-4} \frac{V}{K})$		-0.092	\nearrow	0 \nearrow	0.094 \nearrow	1.657 \nearrow
Pt ($10^{-2} V$)		-1.311	\searrow	-1.340 \searrow	-1.368 \searrow	-1.5424 \nearrow
						-1.5420 \nearrow

In the degenerate Cd- $x(x)$ -alloy, for $N = 2 \times N_{Cd_p}(r_{Cd}) = 3.3855772 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	\nearrow	91.1	93.080853	95.08	126.660914	126.79
ξ_p	\searrow	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$		-1.562	\searrow	-1.563 \nearrow	-1.562 \nearrow	-1.322 \nearrow
ZT		0.999	\nearrow	1 \searrow	0.998 \searrow	0.715 \searrow
$(ZT)_{Mott}$	\nearrow	0.931	1		1.074	3.290
$VC1 (10^{-4} \frac{V}{K})$		-0.061	\nearrow	0 \nearrow	0.063 \nearrow	1.105 \nearrow

$VC2 \left(10^{-2} \frac{V}{K} \right)$	-0.056	0	0.060	1.399	1.406
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2} V$)	-1.423	-1.455	-1.485	-1.6741	-1.6736

For $x=0.5$,

In the degenerate Ga- $\text{X}(x)$ – alloy, for $N = 2 \times N_{\text{CDP}}(r_{\text{Ga}}) = 1.8101138 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	59.094	60.38253	61.68	82.166267	82.25
ξ_b	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-2} \frac{V}{K} \right)$	-0.036	0	0.039	0.908	0.912
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2} V$)	-0.9230	-0.9438	-0.9634	-1.0860	-1.0857

In the degenerate Mg- $\text{X}(x)$ – alloy, for $N = 2 \times N_{\text{CDP}}(r_{\text{Mg}}) = 2.1383444 \times 10^{18} \text{ cm}^{-3}$, one gets

T(K)	66.039	67.477525	68.929	91.82087	91.915
ξ_b	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-2} \frac{V}{K} \right)$	-0.040	0	0.043	1.014	1.019
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2} V$)	-1.0315	-1.0547	-1.0767	-1.2136	-1.2133

In the degenerate In- $\text{X}(x)$ – alloy, for $N = 2 \times N_{\text{CDP}}(r_{\text{In}}) = 2.37166 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	70.759	72.300673	73.85	98.384025	98.484
ξ_b	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-2} \frac{V}{K} \right)$	-0.043	0	0.046	1.087	1.092
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2} V$)	-1.1052	-1.1300	-1.1535	-1.3003	-1.3000

In the degenerate Cd- $\text{X}(x)$ – alloy, for $N = 2 \times N_{\text{CDP}}(r_{\text{Cd}}) = 2.6818126 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	76.801	78.474097	80.162	106.78459	106.894
ξ_b	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-2} \frac{V}{K} \right)$	-0.047	0	0.050	1.180	1.185
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663

Pt ($10^{-2}V$)	-1.1996	-1.2265	-1.2521	-1.4114	-1.4110
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For $x=1$,

In the degenerate Ga- $x(x)$ – alloy, for $N = 2 \times N_{CD_p}(r_{Ga}) = 1.4673047 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	50.605	51.70793	52.821	70.3622	70.434
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mg_{st}}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-2} \frac{V}{K})$	-0.031	0	0.033	0.777	0.781
$T_s(10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2}V$)	-0.7904	-0.8082	-0.8251	-0.9300	-0.9297

In the degenerate Mg- $x(x)$ – alloy, for $N = 2 \times N_{CD_p}(r_{Mg}) = 1.7333732 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	56.551	57.783653	59.026	78.629815	78.7104
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mg_{st}}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-2} \frac{V}{K})$	-0.035	0	0.037	0.869	0.873
$T_s(10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2}V$)	-0.8833	-0.9031	-0.9220	-1.0392	-1.0390

In the degenerate In- $x(x)$ – alloy, for $N = 2 \times N_{CD_p}(r_{In}) = 1.9225022 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	60.594	61.913901	63.246	84.2501	84.336
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mg_{st}}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-2} \frac{V}{K})$	-0.037	0	0.040	0.931	0.935
$T_s(10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2}V$)	-0.9465	-0.9677	-0.9879	-1.1135	-1.1132

In the degenerate Cd- $x(x)$ – alloy, for $N = 2 \times N_{CD_p}(r_{Cd}) = 2.1739166 \times 10^{18} \text{ cm}^{-3}$, one gets:

T(K)	65.768	67.200452	68.647	91.44384	91.538
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mg_{st}}$	0.931	1	1.074	3.290	3.306
$VC1(10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2(10^{-2} \frac{V}{K})$	-0.040	0	0.043	1.010	1.015
$T_s(10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-2}V$)	-1.0273	-1.0503	-1.0723	-1.2086	-1.2083

Table 6n: Here, for a given T and with decreasing N, the reduced Fermi-energy ξ_n decreases, and other thermoelectric coefficients are in variations, as indicated by the arrows as: (increase: ↑, decrease: ↓). One notes here that with increasing T: (i) for $\xi_n \approx 1.8138$, while the numerical results of S present a same minimum $(S)_{\min} (\approx -1.563 \times 10^{-4} \frac{V}{K})$, those of ZT show a same maximum $(ZT)_{\max} = 1$, (ii) for $\xi_n = 1$, those of S, ZT, $(ZT)_{Mott}$, VC1, and T_s present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $-1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$ respectively, and (iii) for $\xi_n \approx 1.8138$, $(ZT)_{Mott} = 1$.

For x=0,

In the degenerate P- X(x) – alloy, for T= 15.5943916 K, one gets:

N (10^{18}cm^{-3}) ↓	2.5488	2.507675	2.4683	2.0437298	2.04253
ξ_n ↓	1.880	1.8138	1.750	1	0.998
S ($10^{-4} \frac{V}{K}$) ↓	-1.562	↓ -1.563	↑ -1.562	↑ -1.322	↑ -1.320
ZT	0.999	↑ 1	0.999	↓ 0.715	↓ 0.713
$(ZT)_{Mott}$ ↑	0.931	1	1.074	3.290	3.305
VC1 ($10^{-4} \frac{V}{K}$) ↑	-0.061	↑ 0	0.063	↑ 1.105	↑ 1.109
VC2 ($10^{-4} \frac{V}{K}$) ↑	-0.955	↑ 0	0.980	↑ 17.231	↑ 17.294
T_s ($10^{-4} \frac{V}{K}$) ↑	-0.092	↑ 0	0.094	↑ 1.657	↑ 1.663
Pt ($10^{-3} V$)	-2.436	↓ -2.437	↑ -2.436	↑ -2.0611	↑ -2.0585

In the degenerate As- X(x) – alloy, for T= 16.244123 K, one gets:

N (10^{18}cm^{-3}) ↓	2.7098	2.6660176	2.6242	2.1727774	2.1715
ξ_n ↓	1.880	1.8138	1.750	1	0.998
S ($10^{-4} \frac{V}{K}$) ↓	-1.562	↓ -1.563	↑ -1.562	↑ -1.322	↑ -1.320
ZT	0.999	↑ 1	0.999	↓ 0.715	↓ 0.713
$(ZT)_{Mott}$ ↑	0.931	1	1.074	3.290	3.306
VC1 ($10^{-4} \frac{V}{K}$) ↑	-0.061	↑ 0	0.063	↑ 1.105	↑ 1.109
VC2 ($10^{-4} \frac{V}{K}$) ↑	-0.996	↑ 0	1.020	↑ 17.949	↑ 18.015
T_s ($10^{-4} \frac{V}{K}$) ↑	-0.092	↑ 0	0.094	↑ 1.657	↑ 1.663
Pt ($10^{-3} V$)	-2.537	↓ -2.539	↑ -2.537	↑ -2.1470	↑ -2.1442

In the degenerate Sb- X(x) – alloy, for T= 19.917762 K, one gets:

N (10^{18}cm^{-3}) ↓	3.6792	3.619757	3.563	2.95006533	2.94832
ξ_n ↓	1.880	1.8138	1.750	1	0.998
S ($10^{-4} \frac{V}{K}$) ↓	-1.562	↓ -1.563	↑ -1.562	↑ -1.322	↑ -1.320
ZT	0.999	↑ 1	0.999	↓ 0.715	↓ 0.713
$(ZT)_{Mott}$ ↑	0.931	1	1.074	3.290	3.306
VC1 ($10^{-4} \frac{V}{K}$) ↑	-0.061	↑ 0	0.063	↑ 1.105	↑ 1.109
VC2 ($10^{-4} \frac{V}{K}$) ↑	-1.221	↑ 0	1.250	↑ 22.008	↑ 22.089
T_s ($10^{-4} \frac{V}{K}$) ↑	-0.092	↑ 0	0.094	↑ 1.657	↑ 1.663
Pt ($10^{-3} V$)	-3.111	↓ -3.113	↑ -3.111	↑ -2.6325	↑ -2.6291

In the degenerate Sn- X(x) – alloy, for T= 21.8267041 K, one gets:

N (10^{18}cm^{-3}) ↓	4.2206	4.152416	4.0873	3.384177	3.38217
ξ_n ↓	1.880	1.8138	1.750	1	0.998
S ($10^{-4} \frac{V}{K}$) ↓	-1.562	↓ -1.563	↑ -1.562	↑ -1.322	↑ -1.320
ZT	0.999	↑ 1	0.999	↓ 0.715	↓ 0.713
$(ZT)_{Mott}$ ↑	0.931	1	1.074	3.290	3.306
VC1 ($10^{-4} \frac{V}{K}$) ↑	-0.061	↑ 0	0.063	↑ 1.105	↑ 1.109

$VC2 \left(10^{-4} \frac{V}{K} \right)$	-1.338	0	1.370	24.117	24.207
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
$Pt \left(10^{-3} V \right)$	-3.409	-3.411	-3.409	-2.8848	-2.8811

For x=0.5,

In the degenerate P- $X(x)$ – alloy, for T= **11.083436 K**, one gets:

$N \left(10^{18} \text{cm}^{-3} \right)$	1.2096	1.1901097	1.1715	0.9699274	0.96936
ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.677	0	0.694	12.246	12.291
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
$Pt \left(10^{-3} V \right)$	-1.731	-1.732	-1.731	-1.4649	-1.4630

In the degenerate As- $X(x)$ – alloy, for T= **11.5452212 K**, one gets:

$N \left(10^{18} \text{cm}^{-3} \right)$	1.286	1.2652571	1.2454	1.0311717	1.03056
ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.706	0	0.725	12.757	12.804
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
$Pt \left(10^{-3} V \right)$	-1.803	-1.804	-1.803	-1.5259	-1.5240

In the degenerate Sb- $X(x)$ – alloy, for T= **14.156195 K**, one gets:

$N \left(10^{18} \text{cm}^{-3} \right)$	1.7461	1.7178893	1.691	1.40006242	1.39924
ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.868	0	0.887	15.642	15.699
$T_s \left(10^{-4} \frac{V}{K} \right)$	-0.092	0	0.094	1.657	1.663
$Pt \left(10^{-3} V \right)$	-2.211	-2.213	-2.211	-1.8710	-1.8686

In the degenerate Sn- $X(x)$ – alloy, for T= **15.5129421 K** one gets:

$N \left(10^{18} \text{cm}^{-3} \right)$	2.00306	1.9706824	1.9398	1.60608622	1.60514
ξ_m	1.880	1.8138	1.750	1	0.998
$S \left(10^{-4} \frac{V}{K} \right)$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 \left(10^{-4} \frac{V}{K} \right)$	-0.061	0	0.063	1.105	1.109
$VC2 \left(10^{-4} \frac{V}{K} \right)$	-0.951	0	0.973	17.141	17.204

$T_s (10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-2.423	-2.425	-2.423	-2.0503	-2.0477

For x=1,

In the degenerate P- $X(x)$ – alloy, for T=7.7768892 K, one gets:

$N (10^{15} \text{cm}^{-3})$	5.394	5.3071132	5.224	4.3252436	4.3227
ξ_m	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 (10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-4} \frac{V}{K})$	-0.475	0	0.488	8.593	8.625
$T_s (10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.2147	-1.2155	-1.2147	-1.0279	-1.0266

In the degenerate As- $X(x)$ – alloy, for T=8.100909 K, one gets:

$N (10^{15} \text{cm}^{-3})$	5.7346	5.6422212	5.5537	4.5983533	4.5957
ξ_m	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1 (10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-4} \frac{V}{K})$	-0.495	0	0.509	8.951	8.983
$T_s (10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.2654	-1.2662	-1.2654	-1.0707	-1.0693

In the degenerate Sb- $X(x)$ – alloy, for T=9.9329446 K, one gets:

$N (10^{15} \text{cm}^{-3})$	7.7865	7.6606658	7.54021	6.2433652	6.2397
ξ_m	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1 (10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-4} \frac{V}{K})$	-0.609	0	0.625	10.975	11.016
$T_s (10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.5515	-1.5525	-1.5515	-1.3128	-1.3112

In the degenerate Sn- $X(x)$ – alloy, for T=10.8849305 K, one gets:

$N (10^{15} \text{cm}^{-3})$	8.9323	8.7879582	8.64986	7.162097	7.1579
ξ_m	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \frac{V}{K})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.305
$VC1 (10^{-4} \frac{V}{K})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-4} \frac{V}{K})$	-0.667	0	0.685	12.027	12.071
$T_s (10^{-4} \frac{V}{K})$	-0.092	0	0.094	1.657	1.663
Pt ($10^{-3} V$)	-1.7002	-1.7013	-1.7002	-1.4387	-1.4368

Table 6p: Here, for a given T and with decreasing N, the reduced Fermi-energy ξ_p decreases, and other thermoelectric coefficients are in variations, as indicated by the arrows as: (increase: ↑, decrease: ↓). One notes here that with increasing T: (i) for $\xi_p \approx 1.8138$, while the numerical results of S present a same minimum $(S)_{\min} (\approx -1.563 \times 10^{-4} \frac{V}{K})$, those of ZT show a same maximum $(ZT)_{\max} = 1$, (ii) for $\xi_p = 1$, those of S, ZT, $(ZT)_{Mott}$, VC1, and T_s present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $-1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$ respectively, and (iii) for $\xi_p \approx 1.8138$, $(ZT)_{Mott} = 1$.

For x=0,

In the degenerate Ga- X(x) – alloy, for T=71.621813 K, one gets:

N(10^{18}cm^{-3})	2.3226	2.285126	2.2492	1.8623546	1.8613
ξ_p	1.880	1.8138	1.750	1	0.998
S($10^{-4} \frac{V}{K}$)	-1.562	↓	-1.563	↑	-1.562
ZT	0.999	↑	1	↓	0.999
$(ZT)_{Mott}$	0.931	↑	1	↓	1.074
VC1($10^{-4} \frac{V}{K}$)	-0.061	↑	0	↑	0.063
VC2($10^{-2} V$)	-0.044	↑	0	↑	0.045
$T_s (10^{-4} \frac{V}{K})$	-0.092	↑	0	↑	0.094
Pt($10^{-2} V$)	-1.1187	↓	-1.1194	↑	-1.1187
					-0.9466
					-0.9455

In the degenerate Mg- X(x) – alloy, for T= 80.037437 K, one gets:

N(10^{18}cm^{-3})	2.7438	2.6994914	2.6571	2.2000582	2.1988
ξ_p	1.880	1.8138	1.750	1	0.998
S($10^{-4} \frac{V}{K}$)	-1.562	↓	-1.563	↑	-1.562
ZT	0.999	↑	1	↓	0.999
$(ZT)_{Mott}$	0.931	↑	1	↓	1.074
VC1($10^{-4} \frac{V}{K}$)	-0.061	↑	0	↑	0.063
VC2($10^{-2} V$)	-0.049	↑	0	↑	0.050
$T_s (10^{-4} \frac{V}{K})$	-0.092	↑	0	↑	0.094
Pt($10^{-2} V$)	-1.25019	↓	-1.25098	↑	-1.25019
					-1.0578
					-1.0565

In the degenerate In- X(x) – alloy, for T=85.758335 K, one gets:

N(10^{18}cm^{-3})	3.0432	2.9940338	2.947	2.4401073	2.4387
ξ_p	1.880	1.8138	1.750	1	0.998
S($10^{-4} \frac{V}{K}$)	-1.562	↓	-1.563	↑	-1.562
ZT	0.999	↑	1	↓	0.999
$(ZT)_{Mott}$	0.931	↑	1	↓	1.074
VC1($10^{-4} \frac{V}{K}$)	-0.061	↑	0	↑	0.063
VC2($10^{-2} V$)	-0.052	↑	0	↑	0.054
$T_s (10^{-4} \frac{V}{K})$	-0.092	↑	0	↑	0.094
Pt($10^{-2} V$)	-1.339	↓	-1.340	↑	-1.339
					-1.1335
					-1.1320

In the degenerate Cd- X(x) – alloy, for T=93.080853 K, one gets:

N(10^{18}cm^{-3})	3.441	3.3855772	3.3325	2.7592112	2.7576
ξ_p	1.880	1.8138	1.750	1	0.998
S($10^{-4} \frac{V}{K}$)	-1.562	↓	-1.563	↑	-1.562
ZT	0.999	↑	1	↓	0.999
$(ZT)_{Mott}$	0.931	↑	1	↓	1.074
VC1($10^{-4} \frac{V}{K}$)	-0.061	↑	0	↑	0.063
VC2($10^{-2} V$)	-0.057	↑	0	↑	0.058
					1.028
					1.032

$T_s (10^{-4} \text{ V})$	-0.092	0	0.094	1.657	1.663
$Pt (10^{-2} \text{ V})$	-1.454	-1.455	-1.454	-1.2302	-1.2287

For x=0.5,

In the degenerate Ga- $X(x)$ – alloy, for T=60.38253 K, one gets:

$N (10^{18} \text{ cm}^{-3})$	1.8398	1.8101138	1.7817	1.47522446	1.47435
ξ_p	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \text{ V})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 (10^{-4} \text{ V})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-2} \text{ V})$	-0.037	0	0.038	0.667	0.669
$T_s (10^{-4} \text{ V})$	-0.092	0	0.094	1.657	1.663
$Pt (10^{-2} \text{ V})$	-0.9432	-0.9438	-0.9432	-0.7981	-0.7970

In the degenerate Mg- $X(x)$ – alloy, for T=67.477525 K, one gets

$N (10^{18} \text{ cm}^{-3})$	2.1735	2.1383444	2.1048	1.74272905	1.7417
ξ_p	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \text{ V})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 (10^{-4} \text{ V})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-2} \text{ V})$	-0.041	0	0.042	0.745	0.748
$T_s (10^{-4} \text{ V})$	-0.092	0	0.094	1.657	1.663
$Pt (10^{-2} \text{ V})$	-1.0540	-1.0547	-1.0540	-0.8918	-0.8907

In the degenerate In- $X(x)$ – alloy, for T=72.300673 K, one gets:

$N (10^{18} \text{ cm}^{-3})$	2.4106	2.37166	2.3345	1.93287893	1.93173
ξ_p	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \text{ V})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 (10^{-4} \text{ V})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-2} \text{ V})$	-0.044	0	0.045	0.799	0.802
$T_s (10^{-4} \text{ V})$	-0.092	0	0.094	1.657	1.663
$Pt (10^{-2} \text{ V})$	-1.1293	-1.1300	-1.1293	-0.9556	-0.9544

In the degenerate Cd- $X(x)$ – alloy, for T=78.474097 K, one gets:

$N (10^{18} \text{ cm}^{-3})$	2.72588	2.6818126	2.6397	2.18565012	2.18435
ξ_p	1.880	1.8138	1.750	1	0.998
$S (10^{-4} \text{ V})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(ZT)_{Mott}$	0.931	1	1.074	3.290	3.306
$VC1 (10^{-4} \text{ V})$	-0.061	0	0.063	1.105	1.109
$VC2 (10^{-2} \text{ V})$	-0.048	0	0.049	0.867	0.870
$T_s (10^{-4} \text{ V})$	-0.092	0	0.094	1.657	1.663
$Pt (10^{-2} \text{ V})$	-1.2258	-1.2265	-1.2258	-1.0372	-1.0358

For x=1,

In the degenerate Ga- $\text{X}(x)$ – alloy, for T=51.70793 K, one gets:

$N(10^{18}\text{cm}^{-2})$	1.4914	1.4673047	1.4443	1.1958385	1.19513
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4}\frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(\text{ZT})_{\text{Mott}}$	0.931	1	1.074	3.290	3.306
$\text{VC1}(10^{-4}\frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$\text{VC2}(10^{-2}\text{V})$	-0.032	0	0.032	0.571	0.573
$T_s(10^{-4}\frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-2}V)	-0.8077	-0.8082	-0.8077	-0.6834	-0.6825

In the degenerate Mg- $\text{X}(x)$ – alloy, for T=57.783653 K, one gets:

$N(10^{18}\text{cm}^{-2})$	1.7618	1.7333732	1.7062	1.41268163	1.41185
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4}\frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(\text{ZT})_{\text{Mott}}$	0.931	1	1.074	3.290	3.306
$\text{VC1}(10^{-4}\frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$\text{VC2}(10^{-2}\text{V})$	-0.035	0	0.036	0.638	0.641
$T_s(10^{-4}\frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-2}V)	-0.9026	-0.9031	-0.9026	-0.7637	-0.7627

In the degenerate In- $\text{X}(x)$ – alloy, for T=61.913901 K, one gets:

$N(10^{18}\text{cm}^{-2})$	1.95408	1.9225022	1.8923	1.56681981	1.5659
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4}\frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(\text{ZT})_{\text{Mott}}$	0.931	1	1.074	3.290	3.306
$\text{VC1}(10^{-4}\frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$\text{VC2}(10^{-2}\text{V})$	-0.038	0	0.039	0.684	0.687
$T_s(10^{-4}\frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-2}V)	-0.9671	-0.9677	-0.9671	-0.8183	-0.8173

In the degenerate Cd- $\text{X}(x)$ – alloy, for T=67.200452 K, one gets:

$N(10^{18}\text{cm}^{-2})$	2.2096	2.1739166	2.1398	1.77172004	1.7707
ξ_p	1.880	1.8138	1.750	1	0.998
$S(10^{-4}\frac{\text{V}}{\text{K}})$	-1.562	-1.563	-1.562	-1.322	-1.320
ZT	0.999	1	0.999	0.715	0.713
$(\text{ZT})_{\text{Mott}}$	0.931	1	1.074	3.290	3.305
$\text{VC1}(10^{-4}\frac{\text{V}}{\text{K}})$	-0.061	0	0.063	1.105	1.109
$\text{VC2}(10^{-2}\text{V})$	-0.041	0	0.042	0.742	0.745
$T_s(10^{-4}\frac{\text{V}}{\text{K}})$	-0.092	0	0.094	1.657	1.663
Pt (10^{-2}V)	-1.0497	-1.0503	-1.0497	-0.8882	-0.8871